

1024 BIT (256 x 4) STATIC MOS RAM WITH SEPARATE I/O

- 256 x 4 Organization to Meet Needs for Small System Memories
- Access Time — 850 nsec Max.
- Single +5V Supply Voltage
- Directly TTL Compatible — All Inputs and Output
- Static MOS — No Clocks or Refreshing Required
- Simple Memory Expansion — Chip Enable Input
- Inputs Protected — All Inputs Have Protection Against Static Charge
- Low Cost Packaging — 22 Pin Plastic Dual-In-Line Configuration
- Low Power — Typically 150 mW
- Three-State Output — OR-Tie Capability
- Output Disable Provided for Ease of Use in Common Data Bus Systems

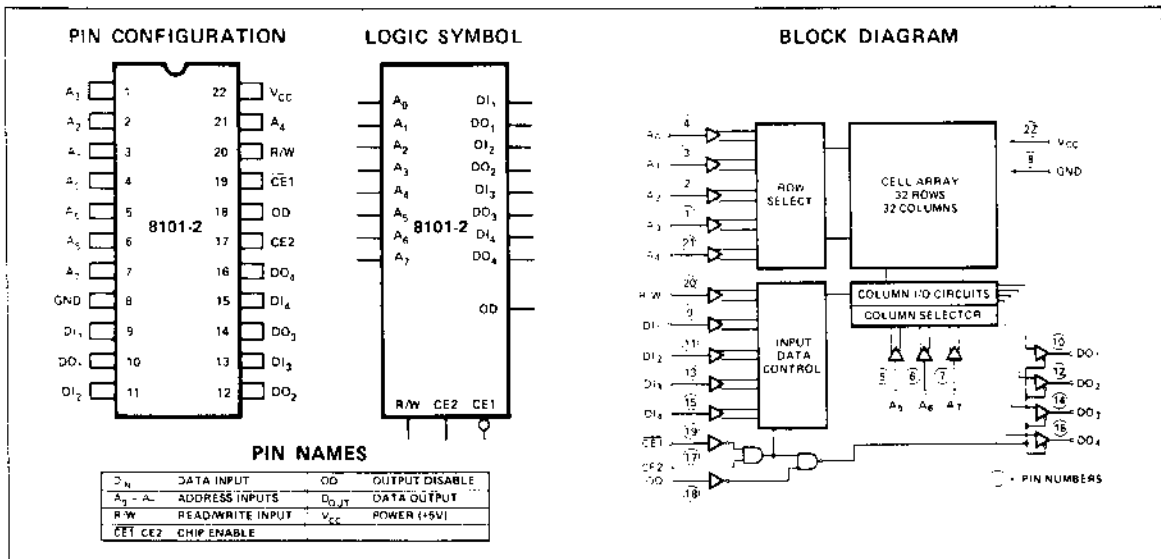
The Intel 8101-2[®] is a 256 word by 4 bit static random access memory element using normally off N-channel MOS devices integrated on a monolithic array. It uses fully DC stable (static) circuitry and therefore requires no clocks or refreshing to operate. The data is read out nondestructively and has the same polarity as the input data.

The 8101-2 is designed for memory applications where high performance, low cost, large bit storage, and simple interfacing are important design objectives.

It is directly TTL compatible in all respects: inputs, outputs, and a single +5V supply. Two chip-enables allow easy selection of an individual package when outputs are OR-tied. An output disable is provided so that data inputs and outputs can be tied for common I/O systems. Output disable is then used to eliminate any bidirectional logic.

The Intel 8101-2 is fabricated with N-channel silicon gate technology. This technology allows the design and production of high performance, easy-to-use MOS circuits and provides a higher functional density on a monolithic chip than either conventional MOS technology or P-channel silicon gate technology.

Intel's silicon gate technology also provides excellent protection against contamination. This permits the use of low cost silicone packaging.



Absolute Maximum Ratings*

Ambient Temperature Under Bias 0°C to 70°C
 Storage Temperature -65°C to +150°C
 Voltage On Any Pin
 With Respect to Ground -0.5V to +7V
 Power Dissipation 1 Watt

***COMMENT:**

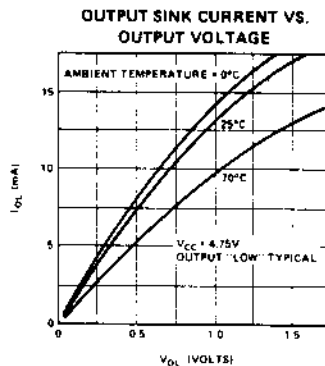
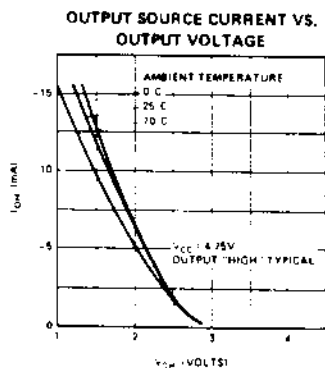
Stresses above those listed under "Absolute Maximum Rating" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. and Operating Characteristics

T_A = 0°C to 70°C, V_{CC} = 5V ±5% unless otherwise specified.

Symbol	Parameter	Min.	Typ. ⁽¹⁾	Max.	Unit	Test Conditions
I _{LI}	Input Current			10	μA	V _{IN} = 0 to 5.25V
I _{LOH}	I/O Leakage Current(2)			15	μA	C _E = 2.2V, V _{OUT} = 4.0V
I _{LOL}	I/O Leakage Current(2)			-50	μA	C _E = 2.2V, V _{OUT} = 0.45V
I _{CC1}	Power Supply Current		30	60	mA	V _{IN} = 5.25V, I _O = 0mA T _A = 25°C
I _{CC2}	Power Supply Current			70	mA	V _{IN} = 5.25V, I _O = 0mA T _A = 0°C
V _{IL}	Input "Low" Voltage	-0.5		+0.65	V	
V _{IH}	Input "High" Voltage	2.2		V _{CC}	V	
V _{OL}	Output "Low" Voltage			+0.45	V	I _{OL} = 2.0mA
V _{OH}	Output "High" Voltage	2.2			V	I _{OH} = -150 μA

NOTE: 1. Typical values are for T_A = 25°C and nominal supply voltage.
 2. Input and Output tied together.



SILICON GATE MOS 8102-2

A.C. CHARACTERISTICS $T_A = 0^\circ\text{C}$ to 70°C , $V_{CC} = 5\text{V} \pm 5\%$ unless otherwise specified

SYMBOL	PARAMETER	LIMITS			UNIT
		MIN.	TYP. (1)	MAX.	
READ CYCLE					
t_{RC}	READ CYCLE	850			ns
t_A	ACCESS TIME		500	850	ns
t_{CO}	CHIP ENABLE TO OUTPUT TIME			500	ns
t_{OH1}	PREVIOUS READ DATA VALID WITH RESPECT TO ADDRESS	50			ns
t_{OH2}	PREVIOUS READ DATA VALID WITH RESPECT TO CHIP ENABLE	0			ns
WRITE CYCLE					
t_{WC}	WRITE CYCLE	850			ns
t_{AW}	ADDRESS TO WRITE SETUP TIME	200			ns
t_{WP}	WRITE PULSE WIDTH	600			ns
t_{WR}	WRITE RECOVERY TIME	50			ns
t_{DW}	DATA SETUP TIME	650			ns
t_{DH}	DATA HOLD TIME	100			ns
t_{CW}	CHIP ENABLE TO WRITE SETUP TIME	750			ns

(1) Typical values are for $T_A = 25^\circ\text{C}$ and nominal supply voltage.

A. C. CONDITIONS OF TEST

Input Pulse Levels: +0.65 Volt to 2.2 Volt

Input Pulse Rise and Fall Times: 20nsec

Timing Measurement Reference Level: 1.5 Volt

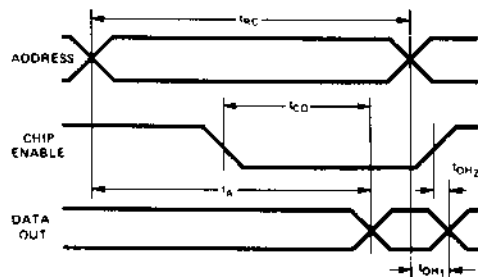
Output Load: 1 TTL Gate and $C_L = 100$ pF

CAPACITANCE $T_A = 25^\circ\text{C}$, $f = 1$ MHz

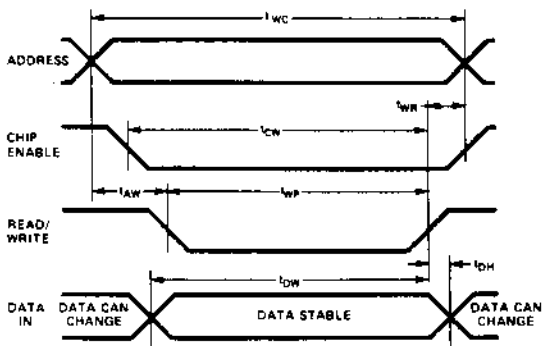
SYMBOL	TEST	LIMITS (pF)	
		TYP.	MAX.
C_{IN}	INPUT CAPACITANCE (ALL INPUT PINS) $V_{IN} = 0\text{V}$	3	5
C_{OUT}	OUTPUT CAPACITANCE $V_{OUT} = 0\text{V}$	7	10

WAVEFORMS

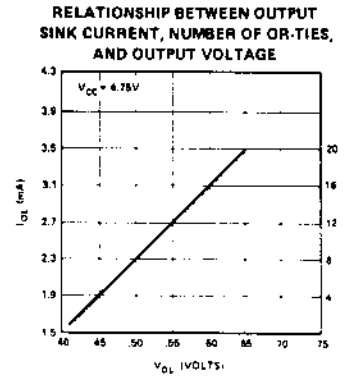
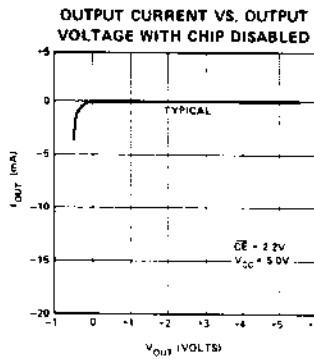
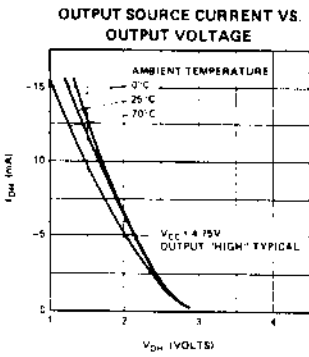
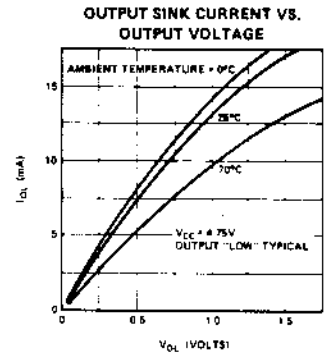
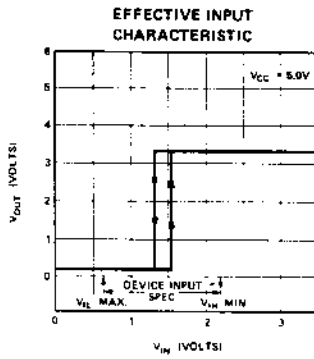
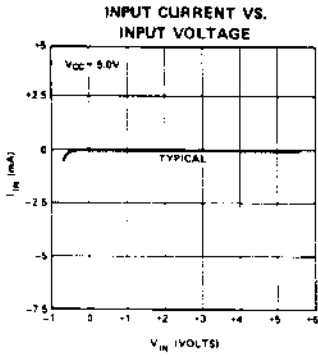
READ CYCLE



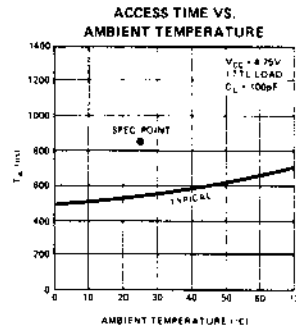
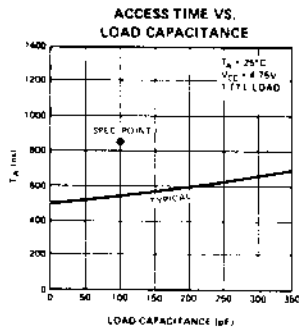
WRITE CYCLE



TYPICAL D.C. CHARACTERISTICS



TYPICAL A.C. CHARACTERISTICS



1024 BIT FULLY DECODED STATIC MOS RANDOM ACCESS MEMORY

- Access Time — 450 ns Max.
- Single +5 Volts Supply Voltage
- Directly TTL Compatible — All Inputs and Output
- Static MOS — No Clocks or Refreshing Required
- Low Power — Typically 150 mW
- Three-State Output — OR-Tie Capability
- Simple Memory Expansion — Chip Enable Input
- Fully Decoded — On Chip Address Decode
- Inputs Protected — All Inputs Have Protection Against Static Charge
- Low Cost Packaging — 16 Pin Plastic Dual-In-Line Configuration

The Intel[®]8102A-4 is a 1024 word by one bit static random access memory element using normally off N-channel MOS devices integrated on a monolithic array. It uses fully DC stable (static) circuitry and therefore requires no clocks or refreshing to operate. The data is read out nondestructively and has the same polarity as the input data.

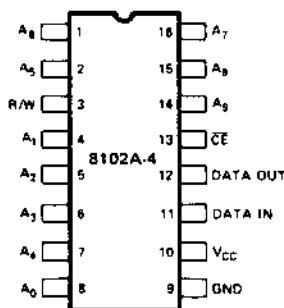
The 8102A-4 is designed for microcomputer memory applications where high performance, low cost, large bit storage, and simple interfacing are important design objectives.

It is directly TTL compatible in all respects: inputs, output, and a single +5 volt supply. A separate chip enable (\overline{CE}) lead allows easy selection of an individual package when outputs are OR-tied.

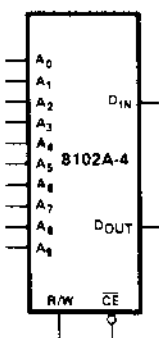
The Intel[®]8102A-4 is fabricated with N-channel silicon gate technology. This technology allows the design and production of high performance, easy-to-use MOS circuits and provides a higher functional density on a monolithic chip than either conventional MOS technology or P-channel silicon gate technology.

Intel's silicon gate technology also provides excellent protection against contamination. This permits the use of low cost silicone packaging.

PIN CONFIGURATION



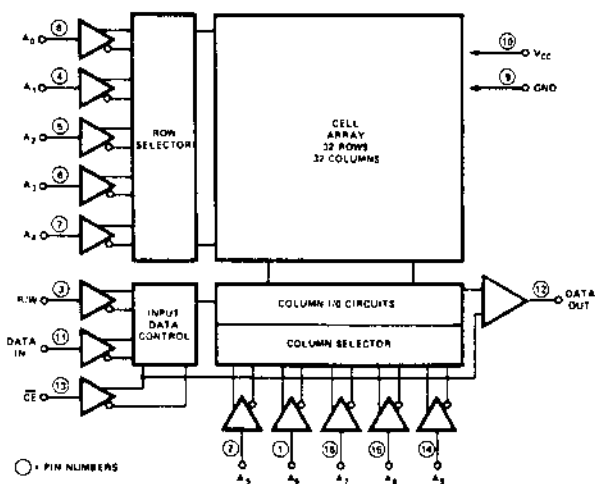
LOGIC SYMBOL



PIN NAMES

D _{IN}	DATA INPUT	\overline{CE}	CHIP ENABLE
A ₀ - A ₉	ADDRESS INPUTS	D _{OUT}	DATA OUTPUT
R/W	READ/WRITE INPUT	V _{CC}	POWER (+5V)

BLOCK DIAGRAM



○ - PIN NUMBERS

ABSOLUTE MAXIMUM RATINGS*

Ambient Temperature Under Bias	0°C to 70°C
Storage Temperature	-65°C to +150°C
Voltage On Any Pin With Respect To Ground	-0.5V to +7V
Power Dissipation	1 Watt

***COMMENT:**

Stresses above those listed under "Absolute Maximum Rating" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. AND OPERATING CHARACTERISTICS

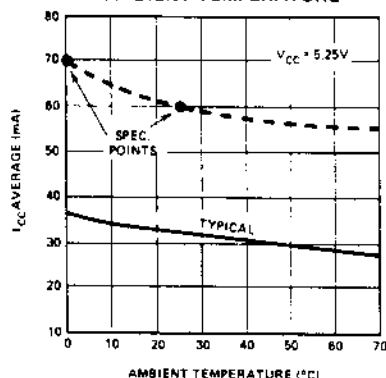
$T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, $V_{CC} = 5V \pm 5\%$ unless otherwise specified

SYMBOL	PARAMETER	LIMITS			UNIT	TEST CONDITIONS
		MIN.	TYP. ⁽¹⁾	MAX.		
I_{LI}	INPUT LOAD CURRENT (ALL INPUT PINS)			10	μA	$V_{IN} = 0$ to $5.25V$
I_{LOH}	OUTPUT LEAKAGE CURRENT			5	μA	$\overline{CE} = 2.0V$, $V_{OUT} = 2.4$ to V_{CC}
I_{LOL}	OUTPUT LEAKAGE CURRENT			-10	μA	$\overline{CE} = 2.0V$, $V_{OUT} = 0.4V$
I_{CC1}	POWER SUPPLY CURRENT		30	60	mA	ALL INPUTS = 5.25V DATA OUT OPEN $T_A = 25^\circ\text{C}$
I_{CC2}	POWER SUPPLY CURRENT			70	mA	ALL INPUTS = 5.25V DATA OUT OPEN $T_A = 0^\circ\text{C}$
V_{IL}	INPUT "LOW" VOLTAGE	-0.5		0.8	V	
V_{IH}	INPUT "HIGH" VOLTAGE	2.0		V_{CC}	V	
V_{OL}	OUTPUT "LOW" VOLTAGE			0.4	V	$I_{OL} = 2.1\text{mA}$
V_{OH}	OUTPUT "HIGH" VOLTAGE	2.4			V	$I_{OH} = -100\mu\text{A}$

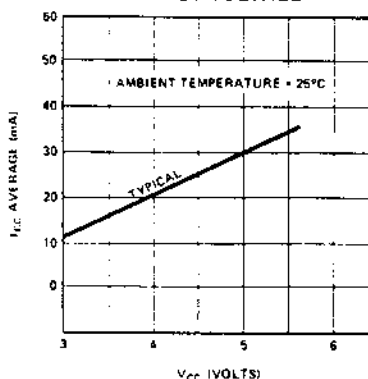
(1) Typical values are for $T_A = 25^\circ\text{C}$ and nominal supply voltage.

TYPICAL D.C. CHARACTERISTICS

POWER SUPPLY CURRENT VS. AMBIENT TEMPERATURE



POWER SUPPLY CURRENT VS. SUPPLY VOLTAGE



A. C. Characteristics $T_A = 0^\circ\text{C}$ to 70°C , $V_{CC} = 5V \pm 5\%$ unless otherwise specified

Symbol	Parameter	Limits			Unit
		Min.	Typ.(1)	Max.	
READ CYCLE					
t_{RC}	Read Cycle	450			ns
t_A	Access Time			450	ns
t_{CO}	Chip Enable to Output Time			230	ns
t_{OH1}	Previous Read Data Valid with Respect to Address	40			ns
t_{OH2}	Previous Read Data Valid with Respect to Chip Enable	0			ns
WRITE CYCLE					
t_{WC}	Write Cycle	450			ns
t_{AW}	Address to Write Setup Time	20			ns
t_{WP}	Write Pulse Width	300			ns
t_{WR}	Write Recovery Time	0			ns
t_{DW}	Data Setup Time	300			ns
t_{DH}	Data Hold Time	0			ns
t_{CW}	Chip Enable to Write Setup Time	300			ns

NOTE: 1. Typical values are for $T_A = 25^\circ\text{C}$ and nominal supply voltage.

A. C. CONDITIONS OF TEST

Input Pulse Levels	0.8 Volt to 2.0 Volt
Input Rise and Fall Times:	10nsec
Timing Measurement	Inputs: 1.5 Volts
Reference Levels	Output: 0.8 and 2.0 Volts
Output Load:	1 TTL Gate and $C_L = 100\text{ pF}$

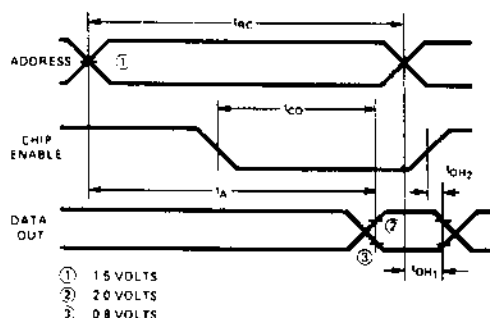
Capacitance^[2] $T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$

SYMBOL	TEST	LIMITS (pF)	
		TYP.[1]	MAX.
C_{IN}	INPUT CAPACITANCE (ALL INPUT PINS) $V_{IN} = 0V$	3	5
C_{OUT}	OUTPUT CAPACITANCE $V_{OUT} = 0V$	7	10

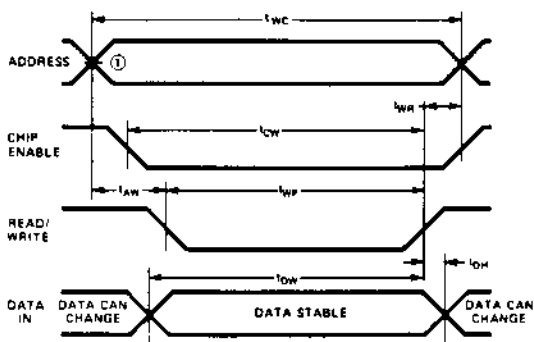
NOTE: 2. This parameter is periodically sampled and is not 100% tested.

Waveforms

READ CYCLE

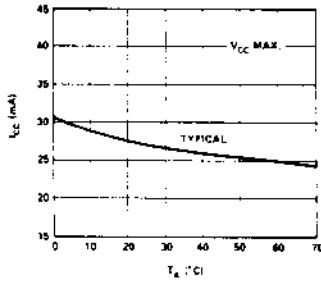


WRITE CYCLE

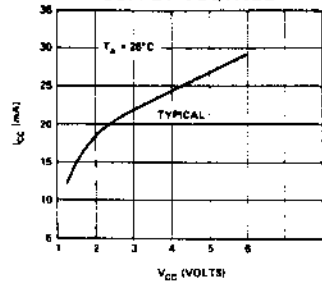


Typical D. C. and A. C. Characteristics

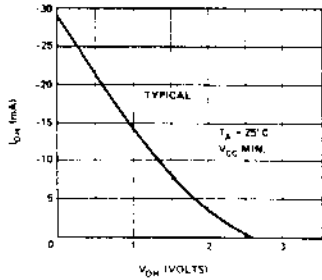
POWER SUPPLY CURRENT VS. AMBIENT TEMPERATURE



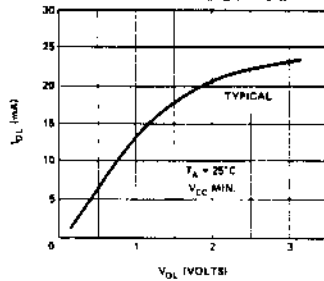
POWER SUPPLY CURRENT VS. SUPPLY VOLTAGE



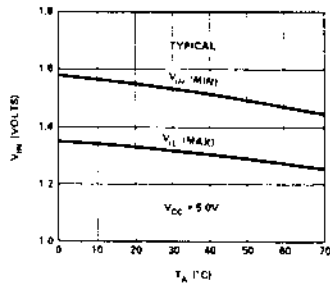
OUTPUT SOURCE CURRENT VS. OUTPUT VOLTAGE



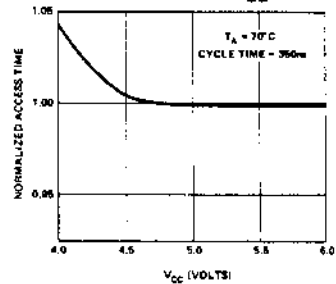
OUTPUT SINK CURRENT VS. OUTPUT VOLTAGE



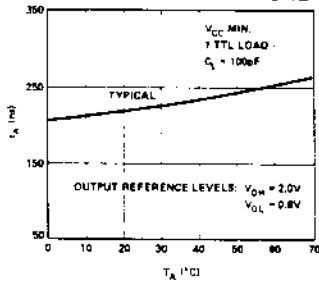
V_{IN} LIMITS VS. TEMPERATURE



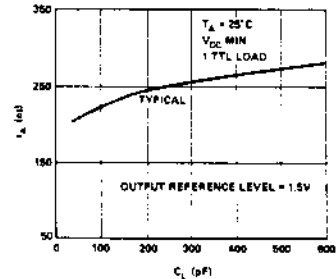
ACCESS TIME VS. V_{CC} NORMALIZED TO V_{CC} = 5.0V



ACCESS TIME VS. AMBIENT TEMPERATURE



ACCESS TIME VS. LOAD CAPACITANCE



FULLY DECODED RANDOM ACCESS 4096 BIT DYNAMIC MEMORY

- * Access Time -- 270 ns max.
- * Read, Write Cycle Times -- 470 ns max.
- * Refresh Period -- 2 ms

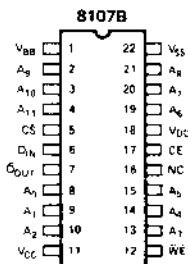
- Low Cost Per Bit
- Low Standby Power
- Easy System Interface
- Only One High Voltage Input Signal – Chip Enable
- TTL Compatible -- All Address, Data, Write Enable, Chip Select Inputs
- Read-Modify-Write Cycle Time -- 590 ns
- Address Registers Incorporated on the Chip
- Simple Memory Expansion – Chip Select Input Lead
- Fully Decoded – On Chip Address Decode
- Output is Three State and TTL Compatible
- Industry Standard 22-Pin Configuration

The Intel 8107B is a 4096 word by 1 bit dynamic n-channel MOS RAM. It was designed for memory applications where very low cost and large bit storage are important design objectives. The 8107B uses dynamic circuitry which reduces the standby power dissipation.

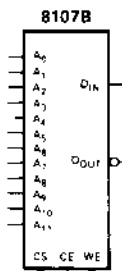
Reading information from the memory is non-destructive. Refreshing is most easily accomplished by performing one read cycle on each of the 64 row addresses. Each row address must be refreshed every two milliseconds. The memory is refreshed whether Chip Select is a logic one or a logic zero.

The 8107B is fabricated with n-channel silicon gate technology. This technology allows the design and production of high performance, easy to use MOS circuits and provides a higher functional density on a monolithic chip than other MOS technologies. The 8107B uses a single transistor cell to achieve high speed and low cost. It is a replacement for the 8107B.

PIN CONFIGURATION



LOGIC SYMBOL

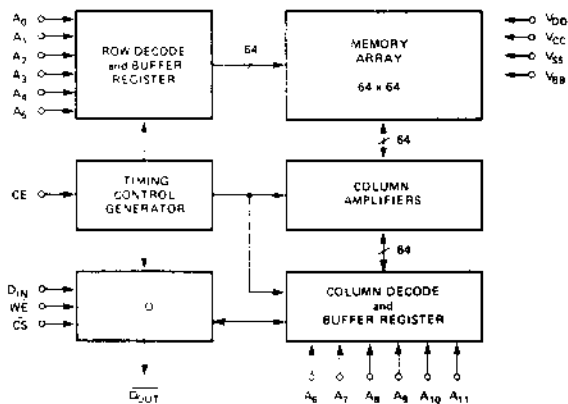


PIN NAMES

A ₀ -A ₁₁	ADDRESS INPUTS*	V _{BB}	POWER (-5V)
CE	CHIP ENABLE	V _{CC}	POWER (+5V)
CS	CHIP SELECT	V _{DD}	POWER (+12V)
D _{IN}	DATA INPUT	V _{SS}	GROUND
D _{OUT}	DATA OUTPUT	WE	WRITE ENABLE
NC	NOT CONNECTED		

*Refresh Address A₀-A₅.

BLOCK DIAGRAM



Absolute Maximum Ratings*

Temperature Under Bias	0°C to 70°C
Storage Temperature	-65°C to +150°C
All Input or Output Voltages with Respect to the most Negative Supply Voltage, V_{BB}	+25V to -0.3V
Supply Voltages V_{DD} , V_{CC} , and V_{SS} with Respect to V_{BB}	+20V to -0.3V
Power Dissipation	1.25W

***COMMENT:**

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. and Operating Characteristics

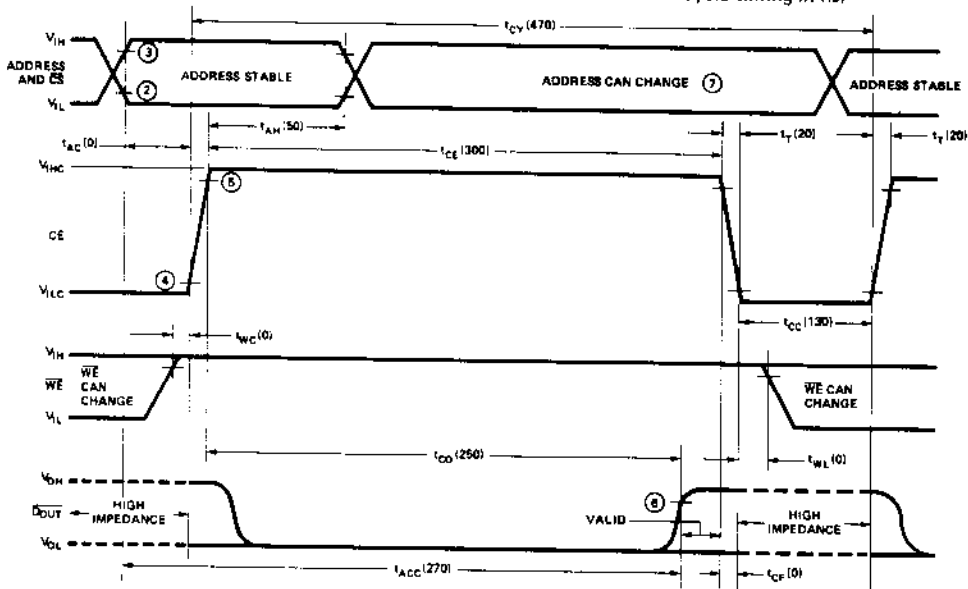
$T_A = 0^\circ\text{C}$ to 70°C , $V_{DD} = +12\text{V} \pm 5\%$, $V_{CC} = +5\text{V} \pm 5\%$, $V_{BB}^{(1)} = -5\text{V} \pm 5\%$, $V_{SS} = 0\text{V}$, unless otherwise noted.

Symbol	Parameter	Limits			Unit	Conditions
		Min.	Typ.[2]	Max.		
I_{LI}	Input Load Current (all inputs except CE)		.01	10	μA	$V_{IN} = V_{IL\text{ MIN}}$ to $V_{IH\text{ MAX}}$
I_{LC}	Input Load Current		.01	10	μA	$V_{IN} = V_{IL\text{ MIN}}$ to $V_{IH\text{ MAX}}$
$ I_{LO} $	Output Leakage Current for high impedance state		.01	10	μA	$CE = V_{ILC}$ or $\overline{CS} = V_{IH}$ $V_O = 0\text{V}$ to 5.25V
I_{DD1}	V_{DD} Supply Current during CE off[3]		110	200	μA	$CE = -1\text{V}$ to $+6\text{V}$
I_{DD2}	V_{DD} Supply Current during CE on		80	100	mA	$CE = V_{IHC}$, $T_A = 25^\circ\text{C}$
I_{DDAV1}	Average V_{DD} Current		55	80	mA	Cycle time = 470ns, $t_{CE} = 300\text{ns}$
I_{DDAV2}	Average V_{DD} Current		27	40	mA	
$I_{CC1}^{(4)}$	V_{CC} Supply Current during CE off		.01	10	μA	$CE = V_{ILC}$ or $\overline{CS} = V_{IH}$
I_{BB}	V_{BB} Supply Current		5	100	μA	
V_{IL}	Input Low Voltage	-1.0		0.6	V	$t_T = 20\text{ns}$ - See Figure 4
V_{IH}	Input High Voltage	2.4		$V_{CC}+1$	V	
V_{ILC}	CE Input Low Voltage	-1.0		+1.0	V	
V_{IHC}	CE Input High Voltage	$V_{DD}-1$		$V_{DD}+1$	V	
V_{OL}	Output Low Voltage	0.0		0.45	V	$I_{OL} = 2.0\text{mA}$
V_{OH}	Output High Voltage	2.4		V_{CC}	V	$I_{OH} = -2.0\text{mA}$

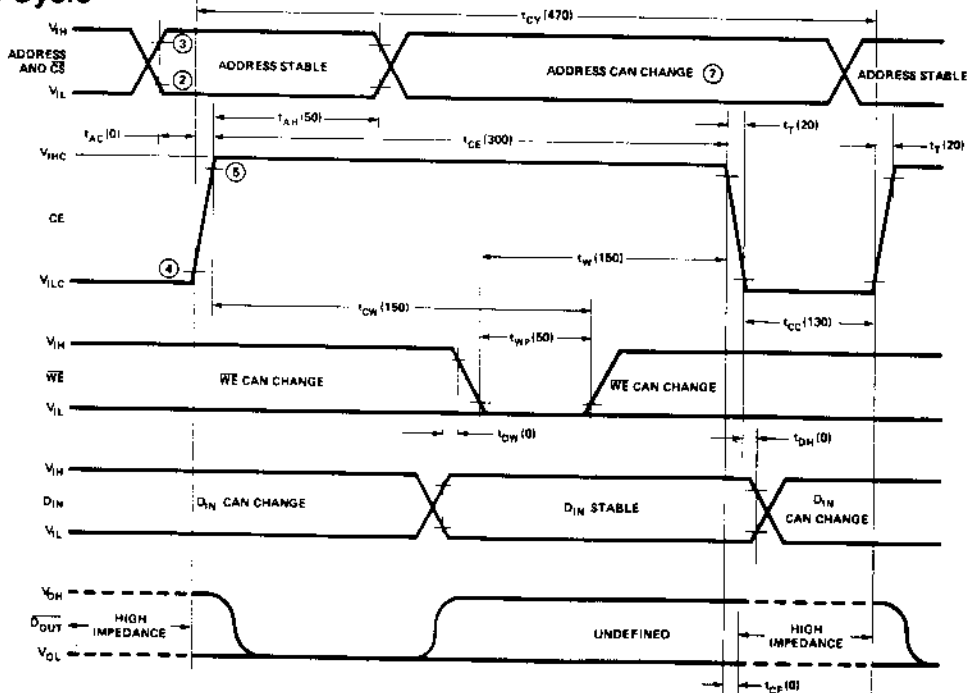
NOTES:

- The only requirement for the sequence of applying voltage to the device is that V_{DD} , V_{CC} , and V_{SS} should never be .3V more negative than V_{BB} .
- Typical values are for $T_A = 25^\circ\text{C}$ and nominal power supply voltages.
- The I_{DD} and I_{CC} currents flow to V_{SS} . The I_{BB} current is the sum of all leakage currents.
- During CE on V_{CC} supply current is dependent on output loading, V_{CC} is connected to output buffer only.

Read and Refresh Cycle ⁽¹⁾ (Numbers in parentheses are for minimum cycle timing in ns)



Write Cycle



- NOTES:
1. For Refresh cycle row and column addresses must be stable before t_{AC} and remain stable for entire t_{AH} period.
 2. $V_{IL\ MAX}$ is the reference level for measuring timing of the addresses, \overline{CS} , \overline{WE} , and D_{IN} .
 3. $V_{IH\ MIN}$ is the reference level for measuring timing of the addresses, \overline{CS} , \overline{WE} , and D_{IN} .
 4. $V_{SS} + 2.0V$ is the reference level for measuring timing of CE.
 5. $V_{DD} - 2V$ is the reference level for measuring timing of CE.
 6. $V_{SS} + 2.0V$ is the reference level for measuring the timing of \overline{DOUT} .
 7. During CE high typically 0.5mA will be drawn from any address pin which is switched from low to high.

SILICON GATE MOS 8107B-4

A. C. Characteristics $T_A = 0^\circ\text{C}$ to 70°C , $V_{DD} = 12\text{V} \pm 5\%$, $V_{CC} = 5\text{V} \pm 10\%$, $V_{BB} = -5\text{V} \pm 5\%$,

READ, WRITE, AND READ MODIFY/WRITE CYCLE $V_{SS} = 0\text{V}$, unless otherwise noted.

Symbol	Parameter	Min.	Max.	Unit	Conditions
t_{REF}	Time Between Refresh		2	ms	t_{AC} is measured from end of address transition
t_{AC}	Address to CE Set Up Time	0		ns	
t_{AH}	Address Hold Time	100		ns	
t_{CC}	CE Off Time	130		ns	
t_T	CE Transition Time	10	40	ns	
t_{CF}	CE Off to Output High Impedance State	0		ns	

READ CYCLE

Symbol	Parameter	Min.	Max.	Unit	Conditions
t_{CY}	Cycle Time	470		ns	$t_T = 20\text{ns}$ $C_{load} = 50\text{pF}$, Load = One TTL Gate, Ref = 2.0V. $t_{ACC} = t_{AC} + t_{CO} + t_T$
t_{CE}	CE On Time	300	4000	ns	
t_{CO}	CE Output Delay		250	ns	
t_{ACC}	Address to Output Access		270	ns	
t_{WL}	CE to \overline{WE}	0		ns	
t_{WC}	\overline{WE} to CE on	0		ns	

WRITE CYCLE

Symbol	Parameter	Min.	Max.	Unit	Conditions
t_{CY}	Cycle Time	470		ns	$t_T = 20\text{ns}$
t_{CE}	CE On Time	300	4000	ns	
t_W	\overline{WE} to CE Off	150		ns	
t_{CW}	CE to \overline{WE}	150		ns	
$t_{DW}^{(2)}$	D_{IN} to \overline{WE} Set Up	0		ns	
t_{DH}	D_{IN} Hold Time	0		ns	
t_{WP}	\overline{WE} Pulse Width	50		ns	

Read Modify Write Cycle

Symbol	Parameter	Min.	Max.	Unit	Conditions
t_{RWC}	Read Modify Write (RMW) Cycle Time	590		ns	$t_T = 20\text{ns}$ $C_{load} = 50\text{pF}$, Load = One TTL Gate, Ref = 2.0V. $t_{ACC} = t_{AC} + t_{CO} + t_T$
t_{CRW}	CE Width During RMW	420	4000	ns	
t_{WC}	\overline{WE} to CE on	0		ns	
t_W	\overline{WE} to CE off	150		ns	
t_{WP}	\overline{WE} Pulse Width	50		ns	
t_{DW}	D_{IN} to \overline{WE} Set Up	0		ns	
t_{DH}	D_{IN} Hold Time	0		ns	
t_{CO}	CE to Output Delay		250	ns	
t_{ACC}	Access Time		270	ns	

Typical Characteristics

Fig. 1. $I_{DD} AV$ VS. TEMPERATURE

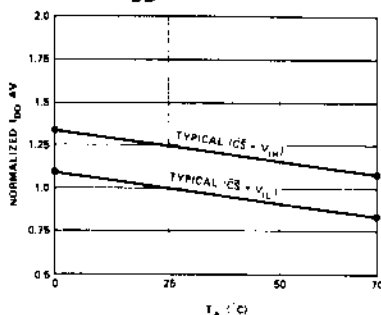


Fig. 2. TYPICAL I_{DD} AVERAGE VS. CYCLE TIME

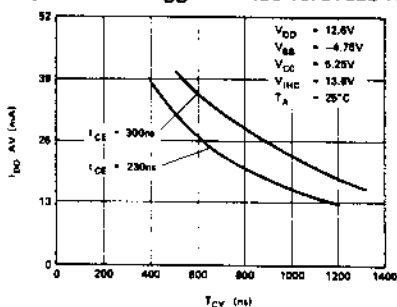


Fig. 3. I_{DD2} VS. TEMPERATURE

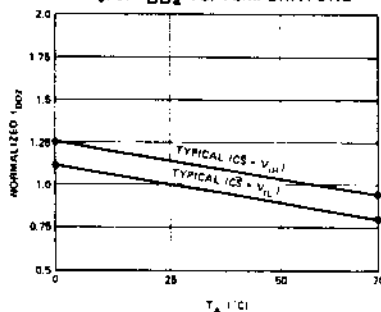


Fig. 4. TYPICAL $V_{IL} MAX$ VS. CE RISE TIME

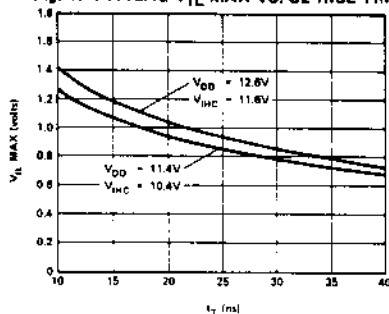


Fig. 5. TYPICAL I_{OH} VS. V_{OH}

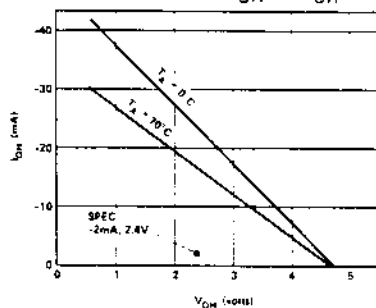


Fig. 6. TYPICAL I_{OL} VS. V_{OL}

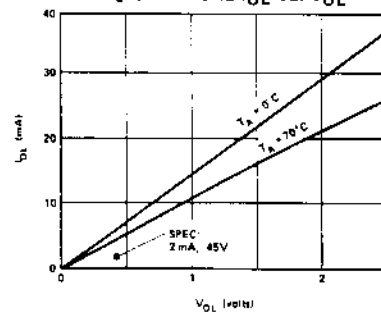


Fig. 7. TYPICAL REFRESH VS. TEMPERATURE

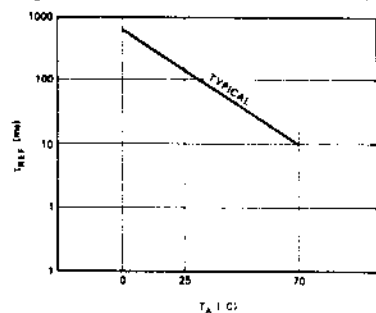
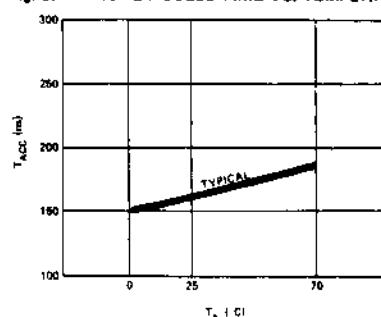


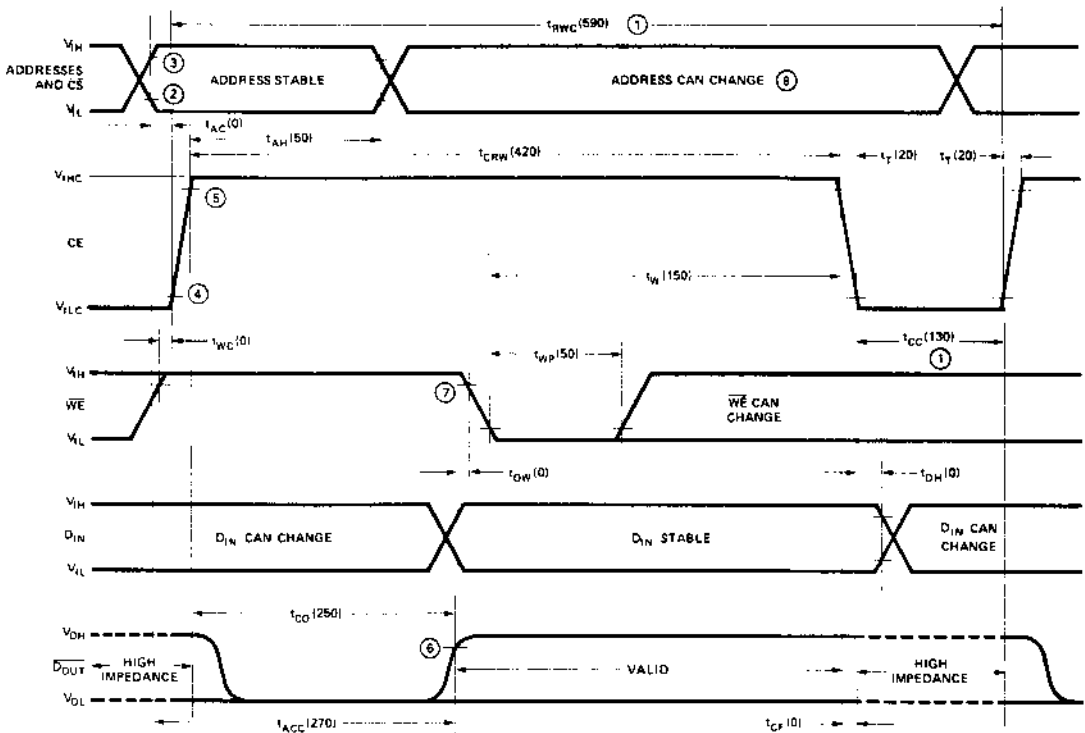
Fig. 8. TYPICAL ACCESS TIME VS. TEMPERATURE



Read Modify Write Cycle ⁽¹⁾

Symbol	Parameter	Min.	Max.	Unit	Conditions	
t_{RWC}	Read Modify Write(RMW) Cycle Time	590		ns	$t_r = 20ns$ $C_{load} = 50pF$, Load = One TTL Gate, Ref = 2.0V	
t_{CRW}	CE Width During RMW	420	3000	ns		
t_{WC}	\overline{WE} to CE on	0		ns		
t_W	\overline{WE} to CE off	150		ns		
t_{WP}	\overline{WE} Pulse Width	50		ns		
t_{DW}	D_{IN} to \overline{WE} Set Up	0		ns		
t_{DH}	D_{IN} Hold Time	0		ns		
t_{CO}	CE to Output Delay		250	ns		
t_{ACC}	Access Time		270	ns		$t_{ACC} = t_{AC} + t_{CO} + t_T$

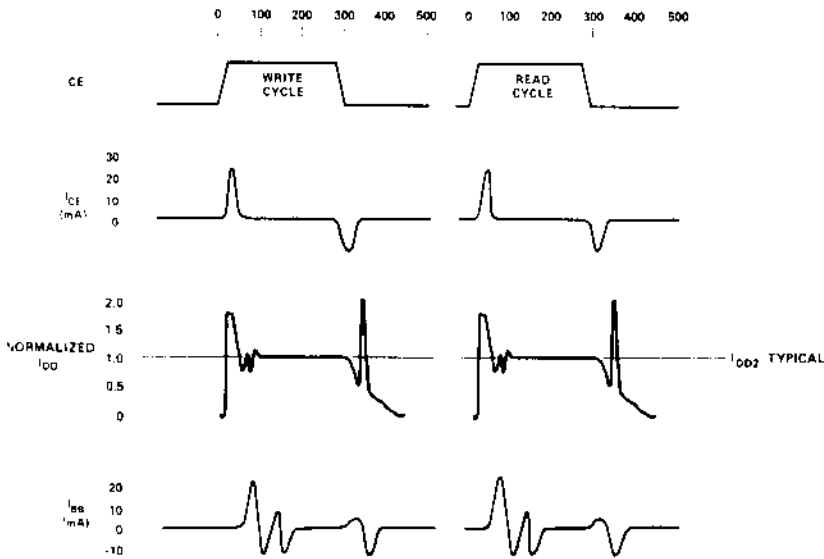
(Numbers in parentheses are for minimum cycle timing in ns.)



NOTES:

- A.C. characteristics are guaranteed only if cumulative CE on time during t_{REF} is $\leq 65\%$ of t_{REF} . For continuous Read-Modify-Write operation, t_{CO} and t_{RWC} should be increased to at least 185ns and 645ns, respectively.
- $V_{IL MAX}$ is the reference level for measuring timing of the addresses, \overline{CS} , \overline{WE} , and D_{IN} .
- $V_{IH MIN}$ is the reference level for measuring timing of the addresses, \overline{CS} , \overline{WE} , and D_{IN} .
- $V_{SS} + 2.0V$ is the reference level for measuring timing of CE.
- $V_{DD} - 2V$ is the reference level for measuring timing of CE.
- $V_{SS} + 2.0V$ is the reference level for measuring the timing of $\overline{D_{OUT}}$.
- \overline{WE} must be at V_{IH} until end of t_{CO} .
- During CE high typically 0.5mA will be drawn from any address pin which is switched from low to high.

Typical Current Transients vs. Time



Applications

Refresh

The 8107B-4 is refreshed by either a read cycle, write cycle, or read-modify write cycle. Only the selected row of memory array is refreshed. The row address is selected by the input signals A_0 thru A_5 . Each individual row address must receive at least one refresh cycle within any two milliseconds time period.

If a read cycle is used for refreshing, then the chip select input, \overline{CS} , can be a logic high or a logic low. If a write cycle or read-modify write cycle is used to refresh the device, then \overline{CS} must be a logic high. This will prevent writing into the memory during refresh.

Power Dissipation

The operating power dissipation of a selected device is the sum of $V_{DD} \times I_{DDAV}$ and $V_{BB} \times I_{BB}$. For a cycle of 400ns and t_{CE} of 230ns typical power dissipation is 456mW.

Standby Power

The 8107B-4 is a dynamic RAM therefore when $V_{CE} = V_{ILC}$ very little power is dissipated. In a typical system most devices are in standby with V_{CE} at V_{ILC} . During this time only leakage currents flow (i.e., I_{DD1} , I_{CC1} , I_{BB} , I_{LO} , I_{L1}). The power dissipated during this inactive period is typically 1.4mW. The typical power dissipation required to perform refresh during standby is the refresh duty cycle, 1.3%, multiplied by the operating power dissipation, or 5.9mW. The total power dissipation during standby is then 7.3mW typical.

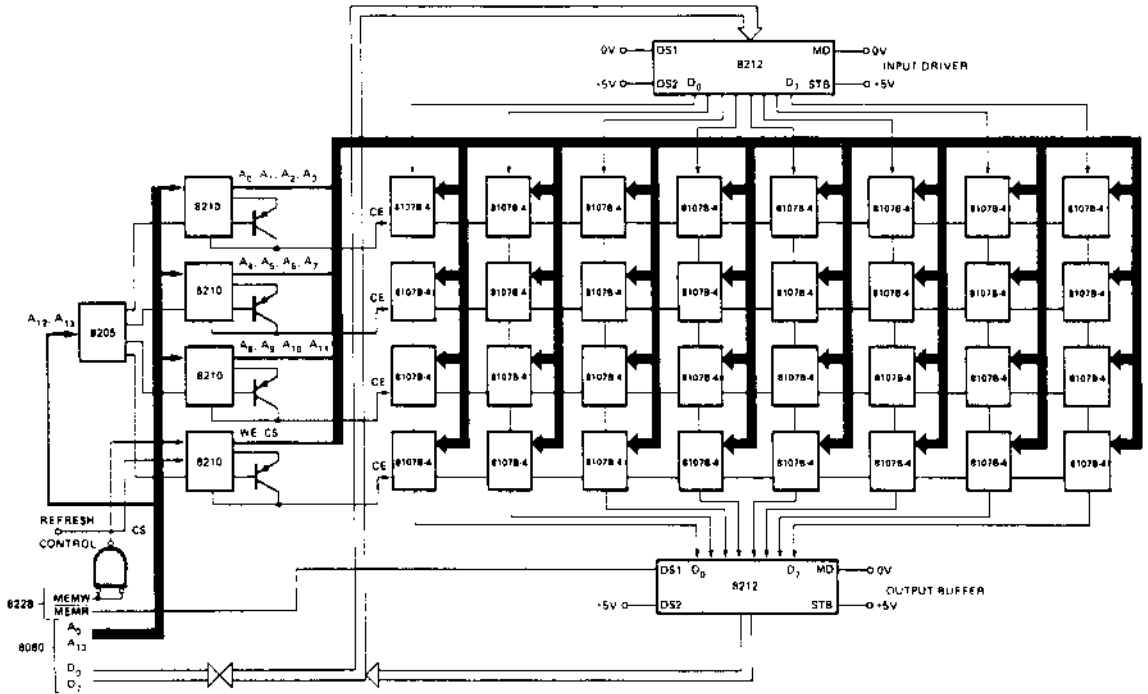
System Interfaces and Filtering

On the following page is an example of a 16K x 8 bit memory system. Device decoding is done with the CE input. All devices are unselected during refresh with \overline{CS} . It is recommended that $1\mu F$ high frequency, low inductance capacitors be used on double sided boards. V_{CC} to V_{SS} decoupling is required only on the devices located around the periphery of the array. For each 36 devices a $100\mu F$ tantalum or equivalent capacitor should be placed from V_{DD} to V_{SS} close to the array.

SILICON GATE MOS 8107B-4

Typical System

Below is an example of a 16K x 8 bit memory circuit. Device decoding is done with the CE input. All devices are unselected during refresh with CS input. The 8210, 8205 and 8212 are standard Intel products.



1024 BIT (256 x 4) STATIC CMOS RAM

***Ultra Low Standby Current: 15 nA/Bit for the 5101**

- **Fast Access Time—650 ns**
- **Single +5 V Power Supply**
- **CE₂ Controls Unconditional Standby Mode**
- **Directly TTL Compatible—All Inputs and Outputs**
- **Three-State Output**

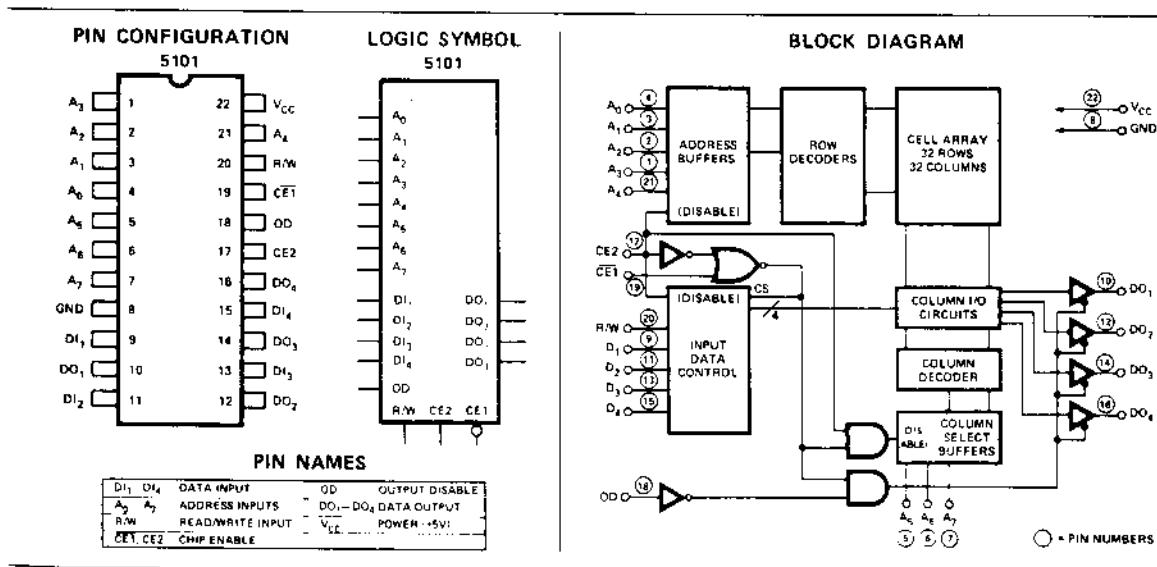
The Intel[®] 5101 and 5101-3 are ultra-low power 1024 bit (256 words x 4-bits) static RAMs fabricated with an advanced ion-implanted silicon gate CMOS technology. The devices have two chip enable inputs. When CE₂ is at a low level, the minimum standby current is drawn by these devices, regardless of any other input transitions on the addresses and other control inputs. Also, when CE₁ is at a high level and address and other control transitions are inhibited, the minimum standby current is drawn by these devices. When in standby the 5101 and 5101-3 draw from the single 5 volt supply only 15 microamps and 200 microamps, respectively. These devices are ideally suited for low power applications where battery operation or battery backup for non-volatility are required.

The 5101 and 5101-3 use fully DC stable (static) circuitry; it is not necessary to pulse chip select for each address transition. The data is read out non-destructively and has the same polarity as the input data. All inputs and outputs are directly TTL compatible. The 5101 and 5101-3 have separate data input and data output terminals. An output disable function is provided so that the data inputs and outputs may be wire OR-ed for use in common data I/O systems.

The 5101L and 5101L-3 are identical to the 5101 and 5101-3, respectively, with the additional feature of guaranteed data retention at a power supply voltage as low as 2.0 volts.

A pin compatible N-channel static RAM, the Intel 2101, is also available for low cost applications where a 256 x 4 organization is needed.

The Intel ion-implanted, silicon gate, complementary MOS (CMOS) allows the design and production of ultra-low power, high performance memories.



SILICON GATE CMOS 5101, 5101-3, 5101L, 5101L-3

Absolute Maximum Ratings *

Ambient Temperature Under Bias	0°C to 70°C
Storage Temperature	-65°C to +150°C
Voltage On Any Pin	
With Respect to Ground	-0.3V to V _{CC} +0.3V
Maximum Power Supply Voltage	+7.0V
Power Dissipation	1 Watt

*COMMENT:

Stresses above those listed under "Absolute Maximum Rating" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D. C. and Operating Characteristics for 5101, 5101-3, 5101L, 5101L-3

T_A = 0°C to 70°C, V_{CC} = 5V ±5% unless otherwise specified.

Symbol	Parameter	Min.	Typ. [1]	Max.	Unit	Test Conditions
I _{LI} [2]	Input Current		5		nA	V _{IN} = 0 to 5.25V
I _{LOH} [2]	Output High Leakage			1	μA	CE1 = 2.2V, V _{OUT} = V _{CC}
I _{LOL} [2]	Output Low Leakage			1	μA	CE1 = 2.2V, V _{OUT} = 0.0V
I _{CC1}	Operating Current		9	22	mA	V _{IN} = V _{CC} Except CE1 ≤ 0.01V Outputs Open
I _{CC2}	Operating Current		13	27	mA	V _{IN} = 2.2V Except CE1 ≤ 0.65V Outputs Open
5101 I _{CCCL} [2]	Standby Current			15	μA	V _{IN} = 0 to V _{CC} , Except CE2 ≤ 0.2V
5101-3 I _{CCCL} [2]	Standby Current			200	μA	V _{IN} = 0 to V _{CC} , Except CE2 ≤ 0.2V
V _{IL}	Input "Low" Voltage	-0.3		0.65	V	
V _{IH}	Input "High" Voltage	2.2		V _{CC}	V	
V _{OL}	Output "Low" Voltage			0.4	V	I _{OL} = 2.0mA
V _{OH}	Output "High" Voltage	2.4			V	I _{OH} = 1.0mA

Low V_{CC} Data Retention Characteristics (For 5101L and 5101L-3) T_A = 0°C to 70°C

Symbol	Parameter	Min.	Typ. [1]	Max.	Unit	Test Conditions
V _{DR}	V _{CC} for Data Retention	2.0			V	
5101L I _{CCDR}	Data Retention Current			15	μA	CE2 ≤ 0.2V V _{DR} = 2.0V
5101L-3 I _{CCDR}	Data Retention Current			200	μA	
t _{CDR}	Chip Deselect to Data Retention Time	0			ns	
t _R	Operation Recovery Time	t _{RC} [3]			ns	

NOTES: 1. Typical values are T_A = 25°C and nominal supply voltage. 2. Current through all inputs and outputs included in I_{CCCL} measurement. 3. t_{RC} = Read Cycle Time.

SILICON GATE CMOS 5101, 5101-3, 5101L, 5101L-3

A.C. Characteristics for 5101, 5101-3, 5101L, 5101L-3

READ CYCLE $T_A = 0^\circ\text{C}$ to 70°C , $V_{CC} = 5\text{V} \pm 5\%$, unless otherwise specified.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
t_{RC}	Read Cycle	650			ns	(See below)
t_A	Access Time			650	ns	
t_{CO1}	Chip Enable (CE1) to Output			600	ns	
t_{CO2}	Chip Enable (CE2) to Output			700	ns	
t_{OD}	Output Disable To Output			350	ns	
t_{DF}	Data Output to High Z State	0		150	ns	
t_{OH1}	Previous Read Data Valid with Respect to Address Change	0			ns	
t_{OH2}	Previous Read Data Valid with Respect to Chip Enable	0			ns	

WRITE CYCLE

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
t_{WC}	Write Cycle	650			ns	(See below)
t_{AW}	Write Delay	150			ns	
t_{CW1}	Chip Enable (CE1) To Write	550			ns	
t_{CW2}	Chip Enable (CE2) To Write	550			ns	
t_{DW}	Data Setup	400			ns	
t_{DH}	Data Hold	100			ns	
t_{WP}	Write Pulse	400			ns	
t_{WR}	Write Recovery	50			ns	
t_{DS}	Output Disable Setup	150			ns	

A. C. CONDITIONS OF TEST

Input Pulse Levels: +0.65 Volt to 2.2 Volt

Input Pulse Rise and Fall Times: 20nsec

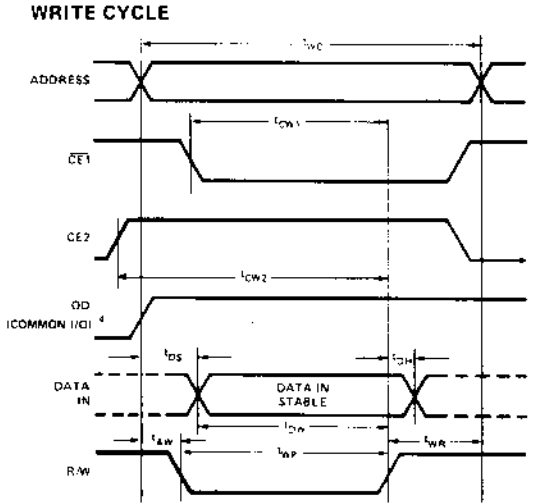
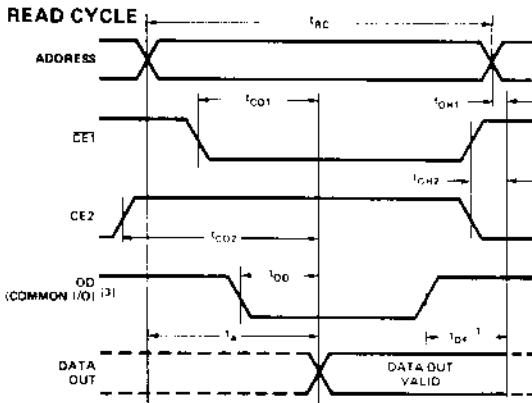
Timing Measurement Reference Level: 1.5 Volt

Output Load: 1 TTL Gate and $C_L = 100\text{pF}$

Capacitance^[2] $T_A = 25^\circ\text{C}$, $f = 1\text{MHz}$

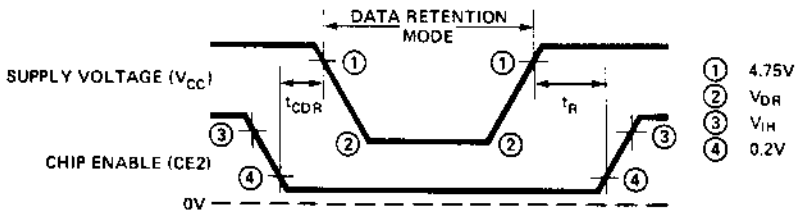
Symbol	Test	Limits (pF)	
		Typ.	Max.
C_{IN}	Input Capacitance (All Input Pins) $V_{IN} = 0\text{V}$	4	8
C_{OUT}	Output Capacitance $V_{OUT} = 0\text{V}$	8	12

Waveforms



- NOTES: 1. Typical values are for $T_A = 25^\circ\text{C}$ and nominal supply voltage.
 2. This parameter is periodically sampled and is not 100% tested.
 3. OD may be tied low for separate I/O operation.
 4. During the write cycle, OD is "high" for common I/O and "don't care" for separate I/O operation.

Low V_{CC} Data Retention



TTL-TO-MOS LEVEL SHIFTER AND HIGH VOLTAGE CLOCK DRIVER

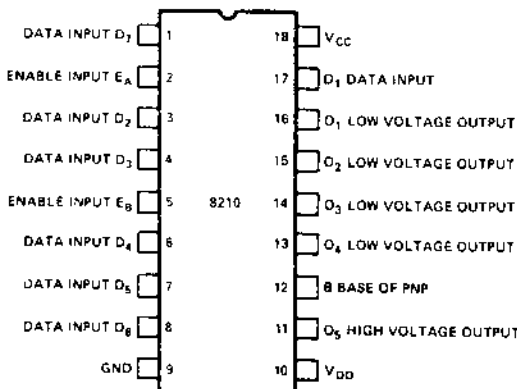
- Four Low Voltage Drivers
- One High Voltage Driver
- TTL and DTL Compatible Inputs
- Outputs Compatible with 8107A MOS Memories
- Operates from Standard Bipolar and MOS Power Supplies
- Maximum MOS Device Protection — Output Clamp Diodes

The Intel[®] 8210 is a Bipolar-to-MOS level shifter and high voltage driver which accepts TTL and DTL inputs. It contains four (4) low voltage drivers and one high voltage driver, each with current driving capabilities suitable for driving N-channel MOS memory devices. The 8210 is particularly suitable for driving the 8107A N-channel MOS memory chips. The 8210 operates from the 5 volt and 12 volt power supplies used to bias the memory devices.

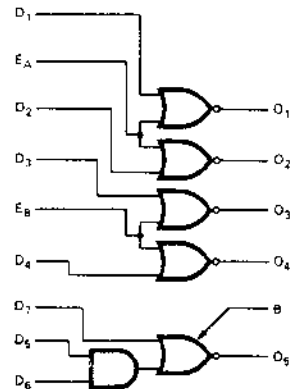
The four low voltage drivers feature two common enable inputs per pair of drivers which permits address or data decoding. The high voltage driver swings the 12 volts required to drive the chip enable (clock) input for the 8107A.

The 8210 high voltage driver requires an externally connected PNP transistor. The PNP base is connected to pin 12, the collector to pin 11, and the emitter to pin 10 or V_{DD} . The use of a fast switching, high voltage, high current gain PNP, like the 2N5057 is recommended.

PIN CONFIGURATION



LOGIC SYMBOL



A.C. Characteristics $T_A = 0^\circ\text{C}$ to 70°C , $V_{CC} = 5.0\text{V} \pm 5\%$, $V_{DD} = 12\text{V} \pm 5\%$

Symbol	Parameter	Min.	Typ.	Max.	Unit
t_{Ld+}	Delay Plus Rise Time for Low Voltage Drivers	5	13	20	ns
t_{Ld-}	Delay Plus Fall Time for Low Voltage Drivers	5	13	20	ns
t_{Hd+}	Delay Plus Rise Time for High Voltage Driver	10	30	40	ns
t_{Hd-}	Delay Plus Fall Time for High Voltage Driver	10	30	40	ns

Capacitance* $T_A = 25^\circ\text{C}$

Symbol	Test	Typ.	Max.
C_{IN}	Input Capacitance	6 pF	12 pF

*This parameter is periodically sampled and is not 100% tested. Condition of measurement is $f = 1\text{ MHz}$, $V_{bias} = 2\text{V}$, $V_{CC} = 0\text{V}$, and $T_A = 25^\circ\text{C}$.

A.C. CONDITIONS OF TEST

Test Load: $C_L = 200\text{ pF}$ for Low Voltage Drivers,

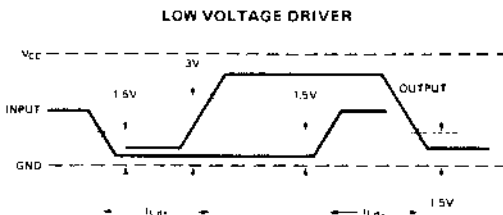
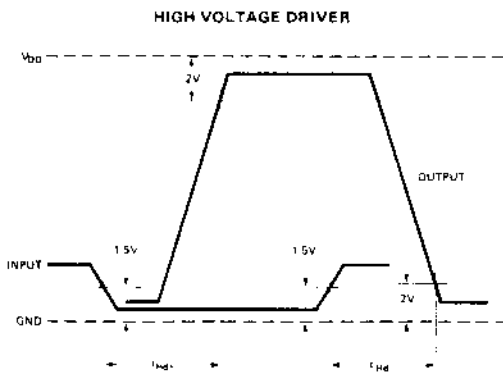
$C_L = 350\text{ pF}$ for High Voltage Drivers

Input Pulse Amplitudes: 3.0V

Input Pulse Rise and Fall Times: 5 ns between 1 volt and 2 volts

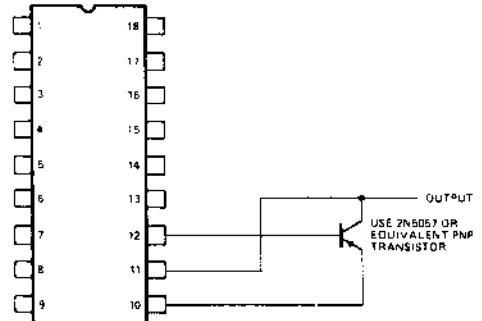
Measurement Points: See Waveforms

Waveforms



Application

HIGH VOLTAGE OUTPUT CONNECTIONS



Absolute Maximum Ratings*

Temperature Under Bias	0°C to 70°C
Storage Temperature	-65°C to +150°C
Supply Voltage, V _{CC}	-0.5 to +7V
Supply Voltage, V _{DD}	-0.5 to +13V

All Input Voltages	-1.0 to +5.5V
Outputs for Low Voltage Drivers	-0.5 to +7V
Outputs for Clock Driver	-1.0 to +13V
Power Dissipation at 25°C	2W

*COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. Characteristics T_A = 0°C to 70°C, V_{CC} = 5.0V ± 5%, V_{DD} = 12V ± 5%

Symbol	Parameter	Min.	Max.	Unit	Test Conditions
I _{FD}	Data Input Load Current		-0.25	mA	V _F = 0.45V
I _{FE}	Enable Input Load Current		-0.50	mA	V _F = 0.45V
I _{RD}	Data Input Leakage Current		10	μA	V _R = 12.6V
I _{RE}	Enable Input Leakage Current		20	μA	V _R = 12.6V
V _{OL}	Output Low Voltage for all Drivers		0.45	V	I _{OL} = 3mA, V _{IH} = 2V
		-1.0		V	I _{OL} = -5mA
V _{OH1}	Output High Voltage for Low Voltage Drivers	V _{CC} - 1.0		V	I _{OH} = -1mA, V _{IL} = 0.8V
			V _{CC} + 1.0	V	I _{OH} = 5mA
V _{OH2}	Output High Voltage for High Voltage Driver	V _{DD} - 0.75		V	I _{OH} = -1mA, V _{IL} = 0.8V
			V _{DD} + 0.5	V	I _{OH} = 5mA
I _{O1}	Pulsed Output Sink Current for Low Voltage Drivers	75		mA	V _O = 2V, V _{IH} = 2V
I _{O2}	Pulsed Output Sink Current for High Voltage Driver	100		mA	V _O = 3V, V _{IH} = 2V
I _{O3}	Pulsed Output Source Current for Low Voltage Drivers	-75		mA	V _O = V _{CC} - 1.5V, V _{IL} = 0.8V
I _{O4}	Pulsed Output Source Current for High Voltage Driver	-100		mA	V _O = V _{DD} - 3V, V _{IL} = 0.8V
V _{IL}	Input Low Voltage, All Inputs		0.8	V	
V _{IH}	Input High Voltage, All Inputs	2		V	

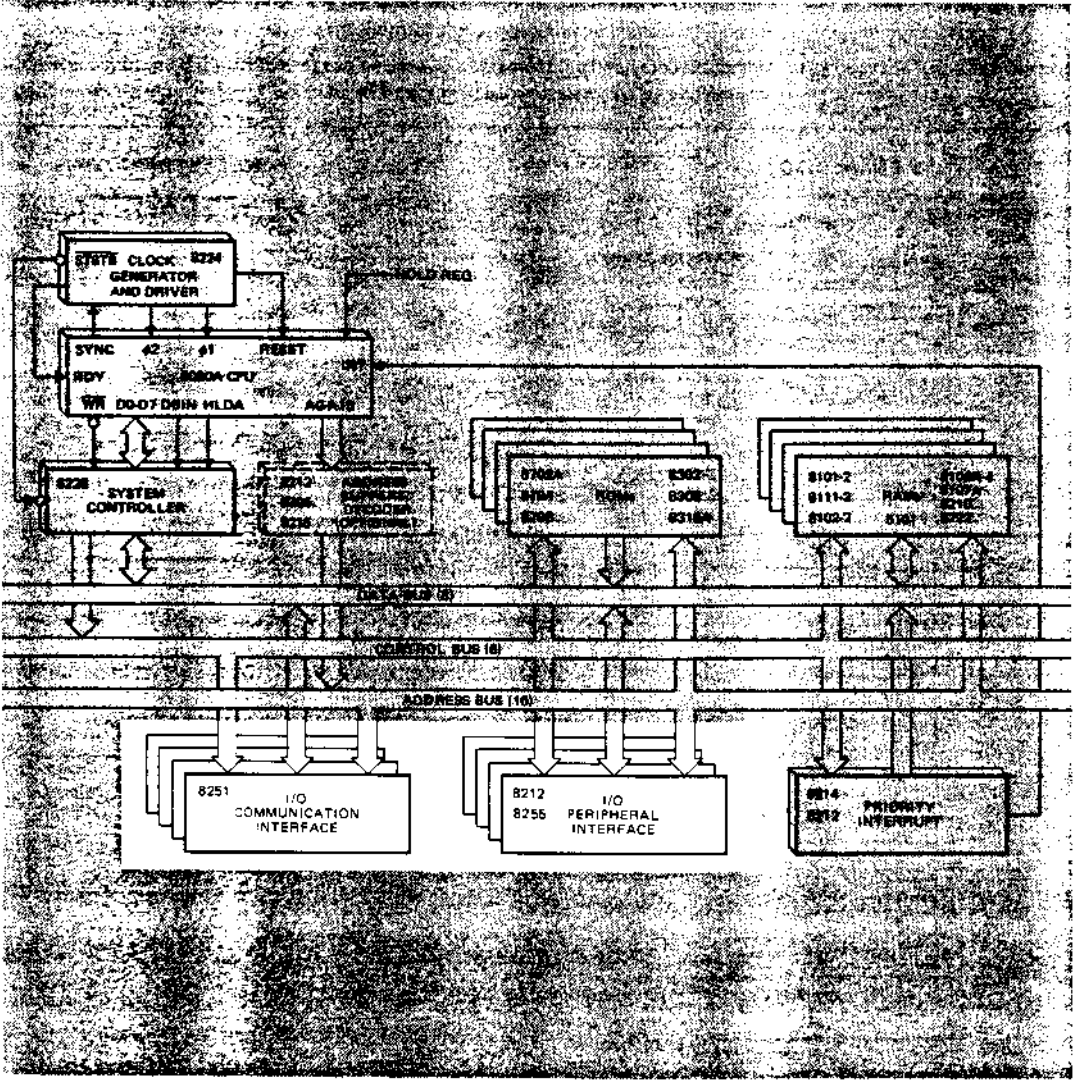
POWER SUPPLY CURRENT DRAIN AND POWER DISSIPATION

All driver outputs are in the state indicated

Symbol	Parameter	Typ. ⁽¹⁾	Max.	Unit	Test Conditions -- Input states to ensure the following output states:		Additional Test Conditions
					All Low Voltage Outputs	High Voltage Output	
I _{CC1}	Current from V _{CC}	26	35	mA	Low	Low	V _{CC} = 5.25V, V _{DD} = 12.6V
I _{DD1}	Current from V _{DD}	12	16	mA	Low	Low	
P _{D1}	Power Dissipation	290	390	mW	Low	Low	
I _{CC2}	Current from V _{CC}	21	28	mA	Low	High	
I _{DD2}	Current from V _{DD}	26	35	mA	Low	High	
P _{D2}	Power Dissipation	450	600	mW	Low	High	
I _{CC3}	Current from V _{CC}	19	25	mA	High	Low	
I _{DD3}	Current from V _{DD}	12	16	mA	High	Low	
P _{D3}	Power Dissipation	280	340	mW	High	Low	
I _{CC4}	Current from V _{CC}	14	18	mA	High	High	
I _{DD4}	Current from V _{DD}	26	35	mA	High	High	
P _{D4}	Power Dissipation	410	550	mW	High	High	

(1) This parameter is periodically sampled and is not 100% tested. Condition of measurement is T_A = 25°C, V_{CC} = 5V, V_{DD} = 12V.

I/O
8212
8255
8251



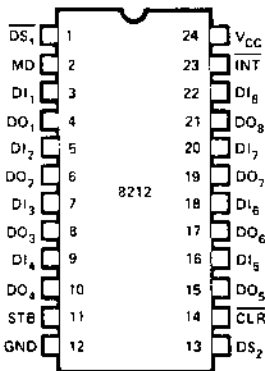
EIGHT-BIT INPUT/OUTPUT PORT

- Fully Parallel 8-Bit Data Register and Buffer
- Service Request Flip-Flop for Interrupt Generation
- Low Input Load Current — .25 mA Max.
- Three State Outputs
- Outputs Sink 15 mA
- 3.65V Output High Voltage for Direct Interface to 8080 CPU or 8008 CPU
- Asynchronous Register Clear
- Replaces Buffers, Latches and Multiplexers in Micro-computer Systems
- Reduces System Package Count

The 8212 input/output port consists of an 8-bit latch with 3-state output buffers along with control and device selection logic. Also included is a service request flip-flop for the generation and control of interrupts to the microprocessor.

The device is multimode in nature. It can be used to implement latches, gated buffers or multiplexers. Thus, all of the principal peripheral and input/output functions of a microcomputer system can be implemented with this device.

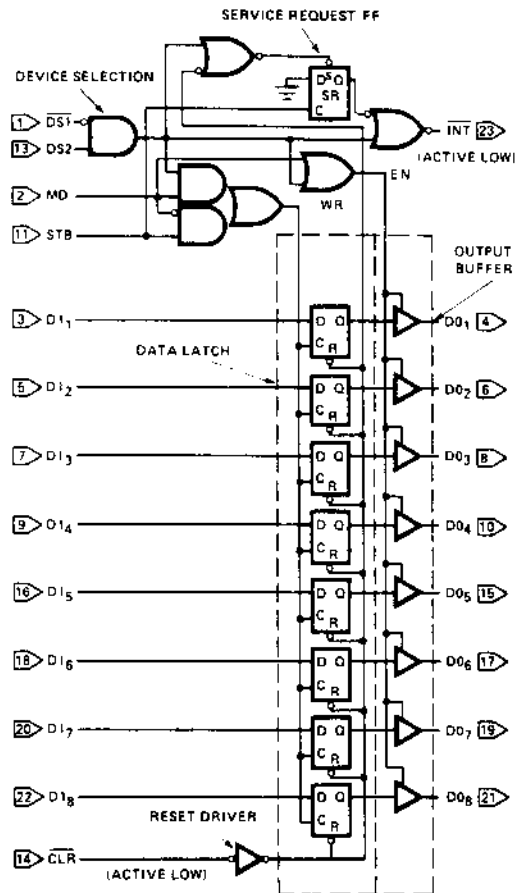
PIN CONFIGURATION



PIN NAMES

DI ₁ -DI ₈	DATA IN
DO ₁ -DO ₈	DATA OUT
DS ₁ , DS ₂	DEVICE SELECT
MD	MODE
STB	STROBE
INT	INTERRUPT (ACTIVE LOW)
CLR	CLEAR (ACTIVE LOW)

LOGIC DIAGRAM



Functional Description

Data Latch

The 8 flip-flops that make up the data latch are of a "D" type design. The output (Q) of the flip-flop will follow the data input (D) while the clock input (C) is high. Latching will occur when the clock (C) returns low.

The data latch is cleared by an asynchronous reset input ($\overline{\text{CLR}}$). (Note: Clock (C) Overrides Reset ($\overline{\text{CLR}}$).)

Output Buffer

The outputs of the data latch (Q) are connected to 3-state, non-inverting output buffers. These buffers have a common control line (EN); this control line either enables the buffer to transmit the data from the outputs of the data latch (Q) or disables the buffer, forcing the output into a high impedance state. (3-state)

This high-impedance state allows the designer to connect the 8212 directly onto the microprocessor bi-directional data bus.

Control Logic

The 8212 has control inputs $\overline{\text{DS1}}$, DS2, MD and STB. These inputs are used to control device selection, data latching, output buffer state and service request flip-flop.

$\overline{\text{DS1}}$, DS2 (Device Select)

These 2 inputs are used for device selection. When $\overline{\text{DS1}}$ is low and DS2 is high ($\overline{\text{DS1}} \cdot \text{DS2}$) the device is selected. In the selected state the output buffer is enabled and the service request flip-flop (SR) is asynchronously set.

MD (Mode)

This input is used to control the state of the output buffer and to determine the source of the clock input (C) to the data latch.

When MD is high (output mode) the output buffers are enabled and the source of clock (C) to the data latch is from the device selection logic ($\overline{\text{DS1}} \cdot \text{DS2}$).

When MD is low (input mode) the output buffer state is determined by the device selection logic ($\overline{\text{DS1}} \cdot \text{DS2}$) and the source of clock (C) to the data latch is the STB (Strobe) input.

STB (Strobe)

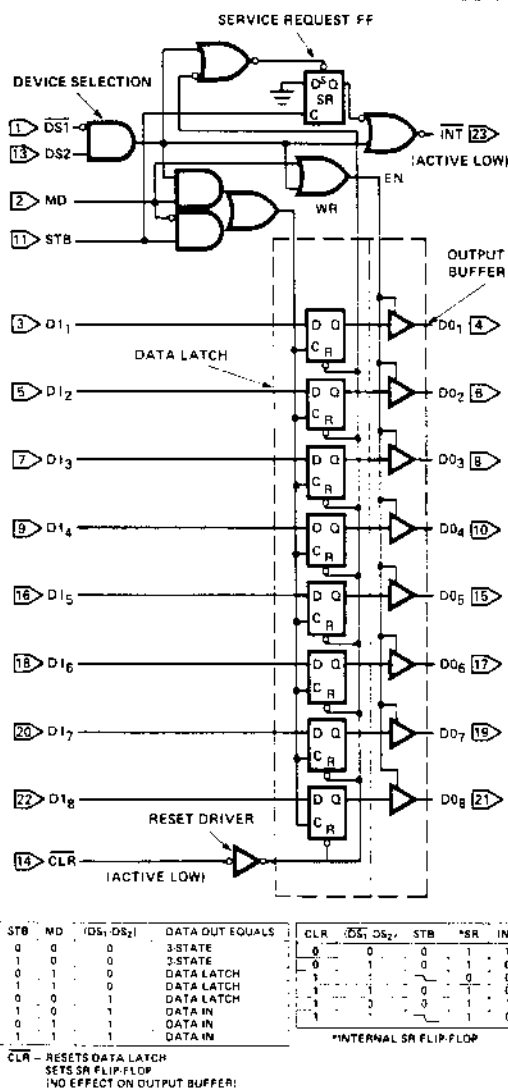
This input is used as the clock (C) to the data latch for the input mode MD = 0 and to synchronously reset the service request flip-flop (SR).

Note that the SR flip-flop is negative edge triggered.

Service Request Flip-Flop

The (SR) flip-flop is used to generate and control interrupts in microcomputer systems. It is asynchronously set by the $\overline{\text{CLR}}$ input (active low). When the (SR) flip-flop is set it is in the non-interrupting state.

The output of the (SR) flip-flop (Q) is connected to an inverting input of a "NOR" gate. The other input to the "NOR" gate is non-inverting and is connected to the device selection logic ($\overline{\text{DS1}} \cdot \text{DS2}$). The output of the "NOR" gate ($\overline{\text{INT}}$) is active low (interrupting state) for connection to active low input priority generating circuits.



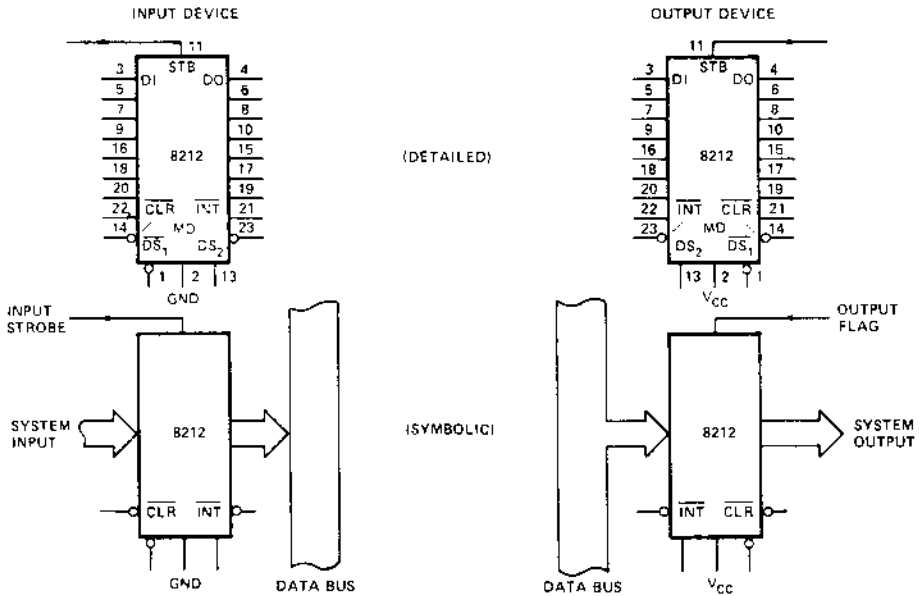
Applications Of The 8212 -- For Microcomputer Systems

- | | | | |
|-----|----------------------------|------|----------------------------|
| I | Basic Schematic Symbol | VII | 8080 Status Latch |
| II | Gated Buffer | VIII | 8008 System |
| III | Bi-Directional Bus Driver | IX | 8080 System: |
| IV | Interrupting Input Port | | 8 Input Ports |
| V | Interrupt Instruction Port | | 8 Output Ports |
| VI | Output Port | | 8 Level Priority Interrupt |

I. Basic Schematic Symbols

Two examples of ways to draw the 8212 on system schematics—(1) the top being the detailed view showing pin numbers, and (2) the bottom being the symbolic view showing the system input or output as a system bus (bus containing 8 parallel lines). The output to the data bus is symbolic in referencing 8 parallel lines.

BASIC SCHEMATIC SYMBOLS



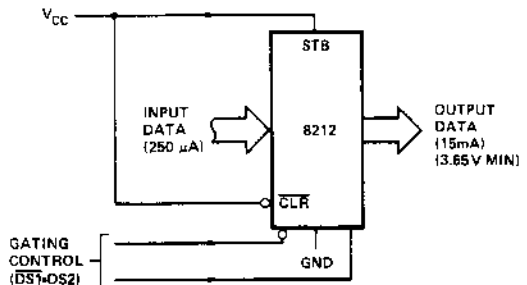
II. Gated Buffer (3- STATE)

The simplest use of the 8212 is that of a gated buffer. By tying the mode signal low and the strobe input high, the data latch is acting as a straight through gate. The output latches are then enabled from the device selection logic \overline{DS}_1 and \overline{DS}_2 .

When the device selection logic is false, the outputs are 3-state.

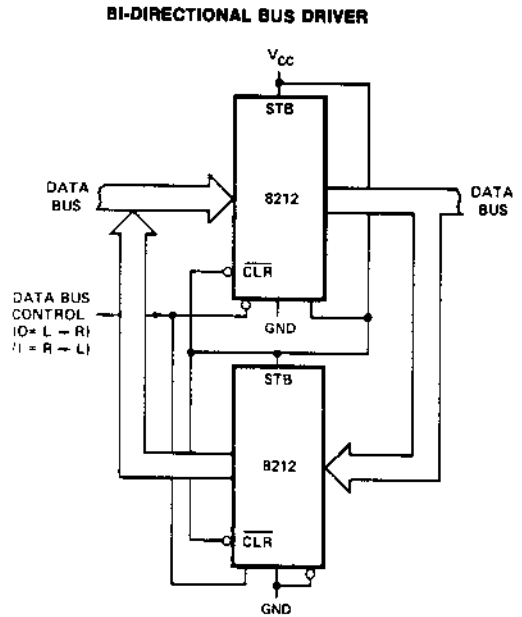
When the device selection logic is true, the input data from the system is directly transferred to the output. The input data load is 250 micro amps. The output data can sink 15 milli amps. The minimum high output is 3.65 volts.

**GATED BUFFER
3-STATE**



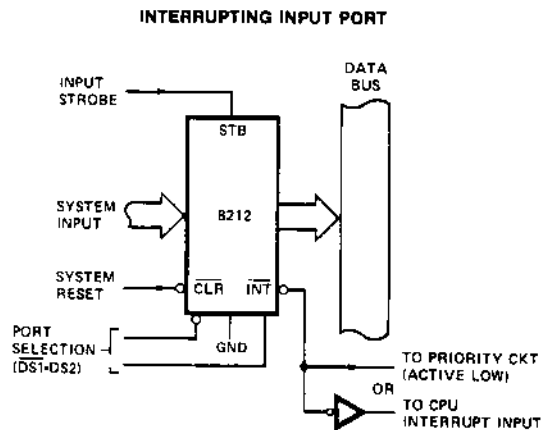
III. Bi-Directional Bus Driver

A pair of 8212's wired (back-to-back) can be used as a symmetrical drive, bi-directional bus driver. The devices are controlled by the data bus input control which is connected to $\overline{DS1}$ on the first 8212 and to $DS2$ on the second. One device is active, and acting as a straight through buffer the other is in 3-state mode. This is a very useful circuit in small system design.



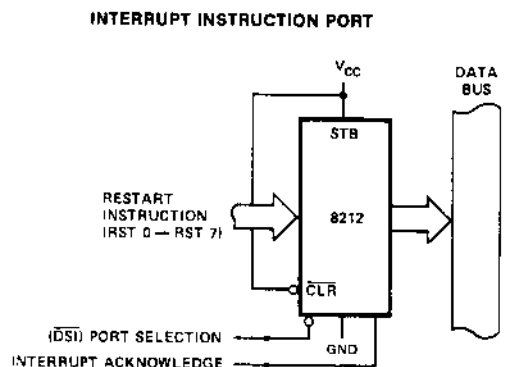
IV. Interrupting Input Port

This use of an 8212 is that of a system input port that accepts a strobe from the system input source, which in turn clears the service request flip-flop and interrupts the processor. The processor then goes through a service routine, identifies the port, and causes the device selection logic to go true — enabling the system input data onto the data bus.



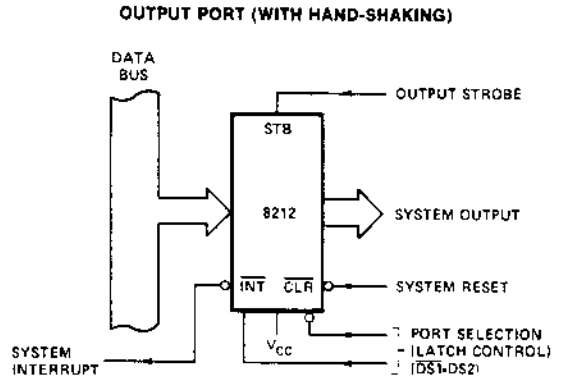
V. Interrupt Instruction Port

The 8212 can be used to gate the interrupt instruction, normally RESTART instructions, onto the data bus. The device is enabled from the interrupt acknowledge signal from the microprocessor and from a port selection signal. This signal is normally tied to ground. ($\overline{DS1}$ could be used to multiplex a variety of interrupt instruction ports onto a common bus).



VI. Output Port (With Hand-Shaking)

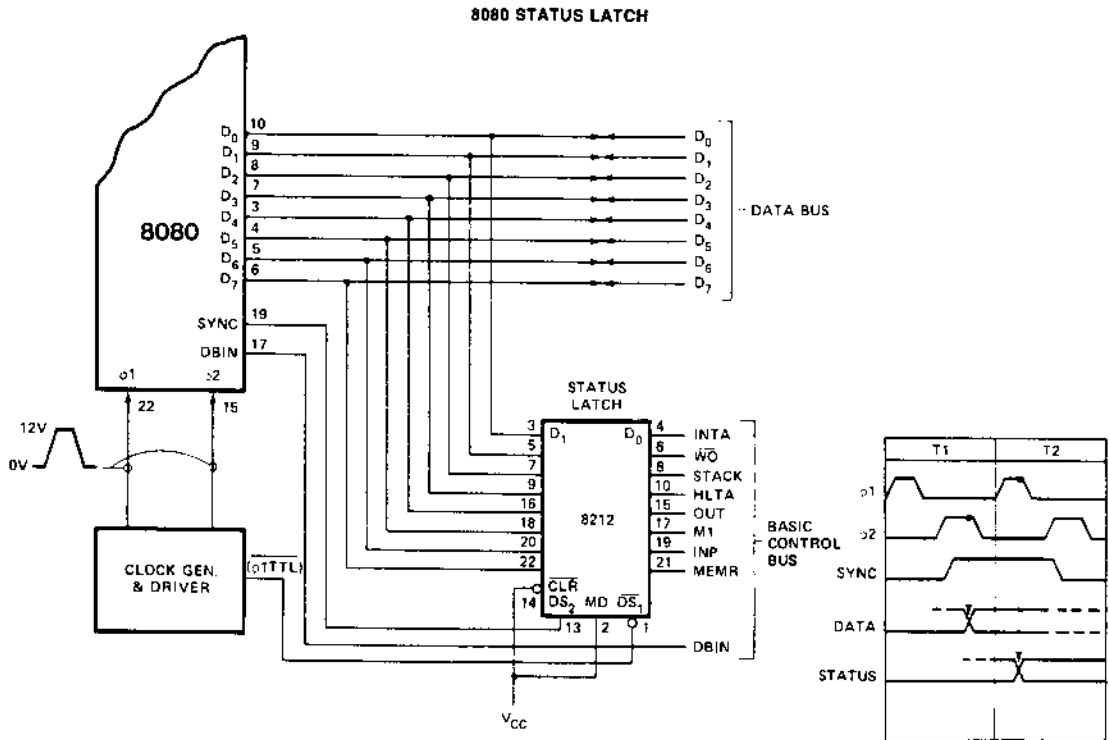
The 8212 can be used to transmit data from the data bus to a system output. The output strobe could be a hand-shaking signal such as "reception of data" from the device that the system is outputting to. It in turn, can interrupt the system signifying the reception of data. The selection of the port comes from the device selection logic. ($\overline{DS1} \cdot DS2$)



VII. 8080 Status Latch

Here the 8212 is used as the status latch for an 8080 microcomputer system. The input to the 8212 latch is directly from the 8080 data bus. Timing shows that when the SYNC signal is true, which is connected to the DS2 input and the phase 1 signal is true, which is a TTL level coming from the clock generator; then, the status data will be latched into the 8212.

Note: The mode signal is tied high so that the output on the latch is active and enabled all the time. It is shown that the two areas of concern are the bidirectional data bus of the microprocessor and the control bus.

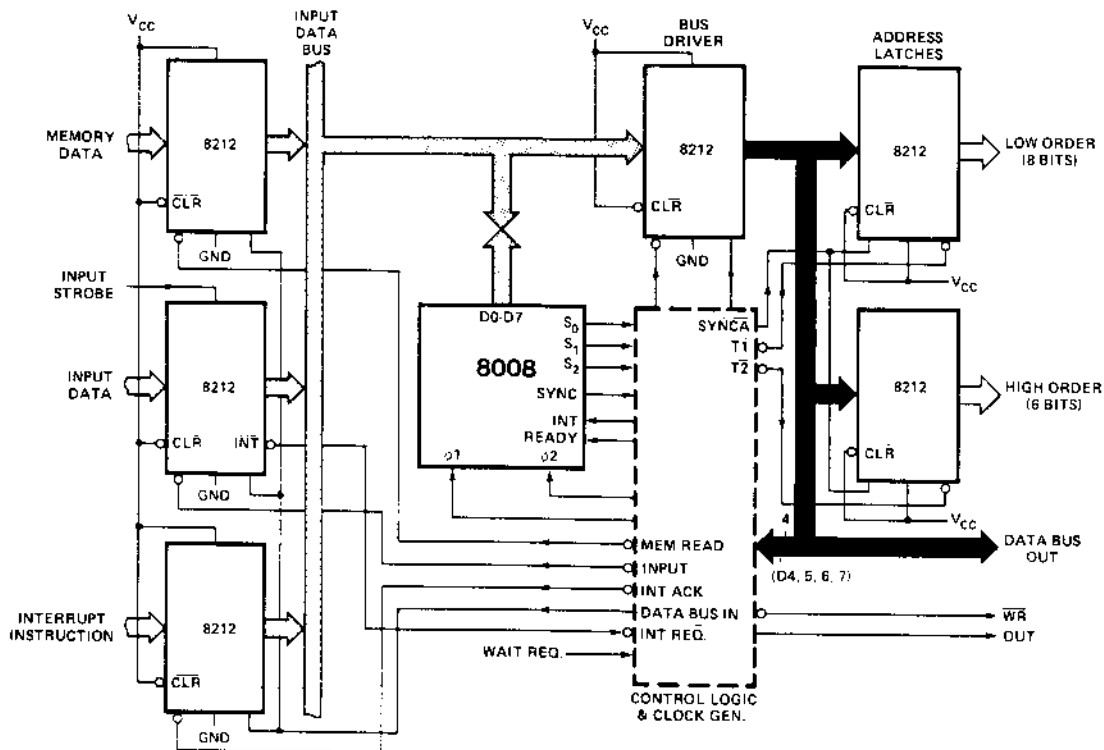


VIII. 8008 System

This shows the 8212 used in an 8008 microcomputer system. They are used to multiplex the data from three different sources onto the 8008 input data bus. The three sources of data are: memory data, input data, and the interrupt instruction. The 8212 is also used as the uni-directional bus driver to provide a proper drive to the address latches (both low order and high order) and to provide adequate drive to the output data bus. The control of these six 8212's in the 8008 system is provided by the control logic and clock generator circuits. These circuits consist of flip-flops, decoders, and gates to generate the control functions necessary for 8008 microcomputer systems. Also note that the input data port has a strobe input. This allows the proces-

sor to be interrupted from the input port directly. The control of the input bus consists of the data bus input signal, control logic, and the appropriate status signal for bus discipline whether memory read, input, or interrupt acknowledge. The combination of these four signals determines which one of these three devices will have access to the input data bus. The bus driver, which is implemented in an 8212, is also controlled by the control logic and clock generator so it can be 3-stated when necessary and also as a control transmission device to the address latches. Note: The address latches can be 3-stated for DMA purposes and they provide 15 milli amps drive, sufficient for large bus systems.

8008 SYSTEM



IX. 8080 System

This drawing shows the 8212 used in the I/O section of an 8080 microcomputer system. The system consists of 8 input ports, 8 output ports, 8 level priority systems, and a bidirectional bus driver. (The data bus within the system is darkened for emphasis). Basically, the operation would be as follows: The 8 ports, for example, could be connected to 8 keyboards, each keyboard having its own priority level. The keyboard could provide a strobe input of its own which would clear the service request flip-flop. The $\overline{\text{INT}}$ signals are connected to an 8 level priority encoding circuit. This circuit provides a positive true level to the central processor (INT) along with a three-bit code to the interrupt instruction port for the generation of RESTART instructions. Once the processor has been interrupted and it acknowledges the reception of the interrupt, the Interrupt Acknowledge signal is generated. This signal transfers data in the form of a RESTART instruction onto the buffered data bus. When the DBIN signal is true this RESTART instruction is gated into the microcomputer, in this case, the 8080 CPU. The 8080 then performs a software controlled interrupt service routine, saving the status of its current operation in the push-down stack and performing an INPUT instruction. The INPUT instruction thus sets the INP status

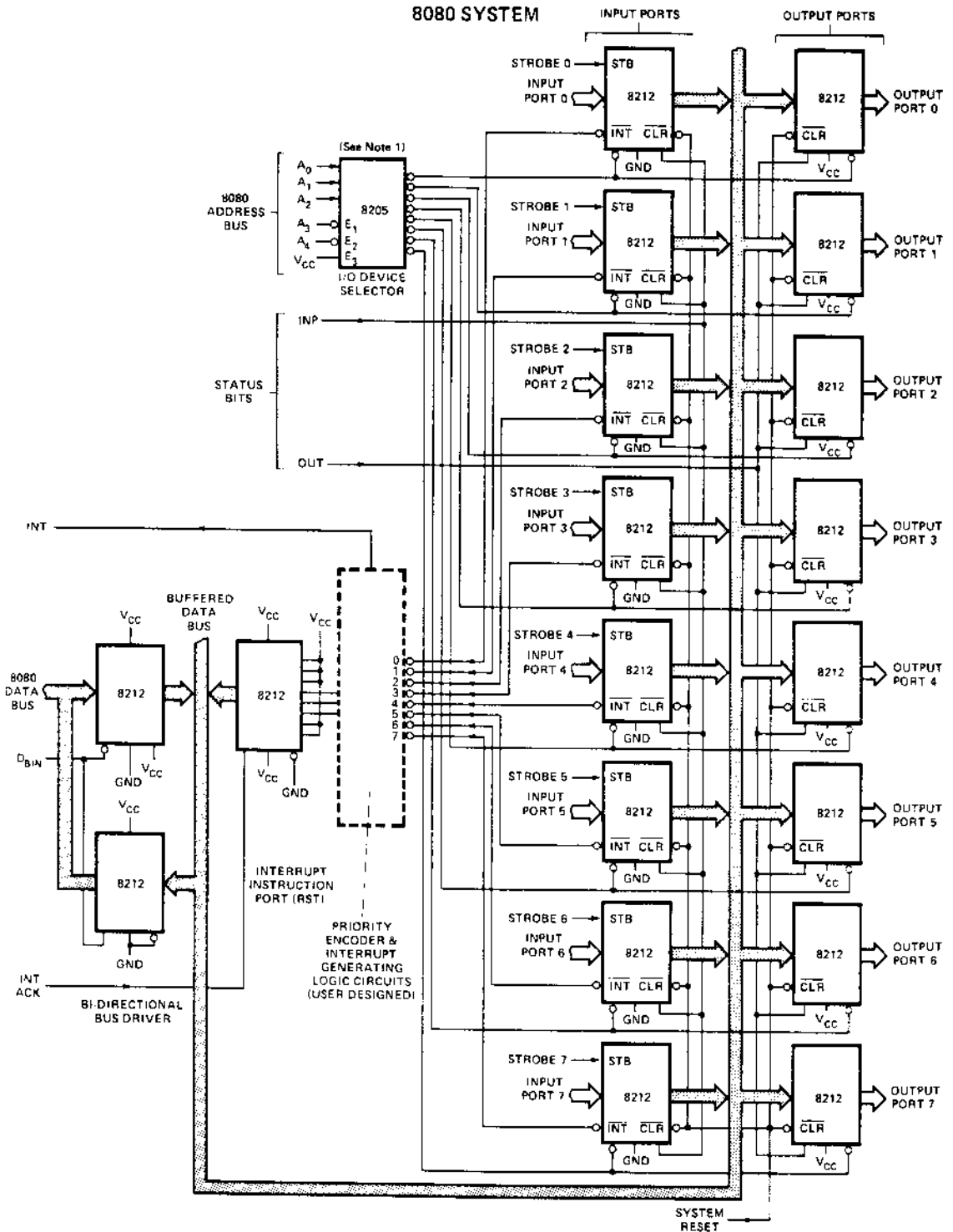
bit, which is common to all input ports.

Also present is the address of the device on the 8080 address bus which in this system is connected to an 8205, one out of eight decoder with active low outputs. These active low outputs will enable one of the input ports, the one that interrupted the processor, to put its data onto the buffered data bus to be transmitted to the CPU when the data bus input signal is true. The processor can also output data from the 8080 data bus to the buffered data bus when the data bus input signal is false. Using the same address selection technique from the 8205 decoder and the output status bit, we can select with this system one of eight output ports to transmit the data to the system's output device structure.

Note: This basic I/O configuration for the 8080 can be expanded to 256 input devices and 256 output devices all using 8212 and, of course, the appropriate decoding.

Note that the 8080 is a 3.3-volt minimum high input requirement and that the 8212 has a 3.65-volt minimum high output providing the designer with a 350 milli volt noise margin worst case for 8080 systems when using the 8212.

8080 SYSTEM



Note 1. This basic I/O configuration for the 8080 can be expanded to 256 input devices and 256 output devices all using 8212 and the appropriate decoding.

SCHOTTKY BIPOLAR 8212

Absolute Maximum Ratings*

Temperature Under Bias Plastic	-65°C to +75°C
Storage Temperature	-65°C to +160°C
All Output or Supply Voltages	-0.5 to +7 Volts
All Input Voltages	-1.0 to 5.5 Volts
Output Currents	125 mA

*COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied.

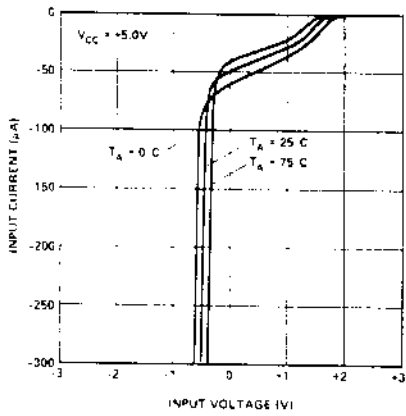
D.C. Characteristics

$T_A = 0^\circ\text{C to } +75^\circ\text{C}$ $V_{CC} = +5\text{V} \pm 5\%$

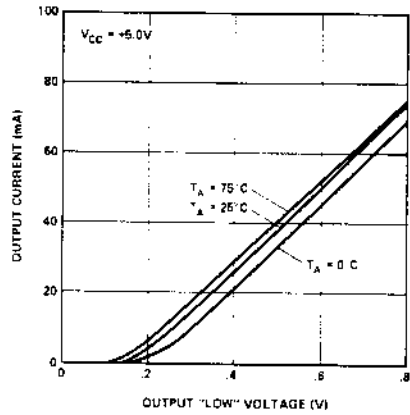
Symbol	Parameter	Limits			Unit	Test Conditions
		Min.	Typ.	Max.		
I_F	Input Load Current ACK, DS ₁ , CR, DI -DI ₃ Inputs			-0.25	mA	$V_F = .45\text{V}$
I_F	Input Load Current MD Input			-0.75	mA	$V_C = .45\text{V}$
I_F	Input Load Current DS ₁ Input			-1.0	mA	$V_F = .45\text{V}$
I_L	Input Leakage Current ACK, DS, CR, DI -DI ₃ Inputs			10	μA	$V_L = 5.25\text{V}$
I_L	Input Leakage Current MO Input			30	μA	$V_L = 5.25\text{V}$
I_L	Input Leakage Current DS ₁ Input			40	μA	$V_L = 5.25\text{V}$
V_C	Input Forward Voltage Clamp			-1	V	$I_C = -5\text{ mA}$
V_{IL}	Input "Low" Voltage			.85	V	
V_{IH}	Input "High" Voltage	2.0			V	
V_{OL}	Output "Low" Voltage			.45	V	$I_{OL} = 15\text{ mA}$
V_{OH}	Output "High" Voltage	3.65	4.0		V	$I_{OH} = -1\text{ mA}$
I_{SC}	Short Circuit Output Current	-15		-75	mA	$V_O = 0\text{ V}$
$ I_O $	Output Leakage Current High Impedance State			20	μA	$V_O = .45\text{V}/5.25\text{V}$
I_{CC}	Power Supply Current		90	130	mA	

Typical Characteristics

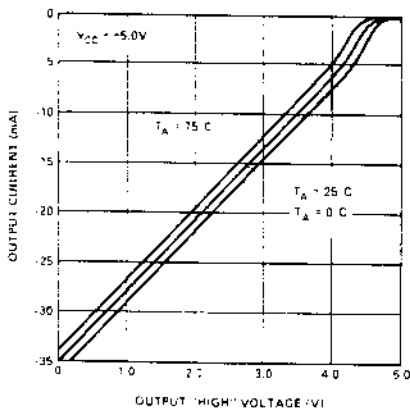
INPUT CURRENT VS. INPUT VOLTAGE



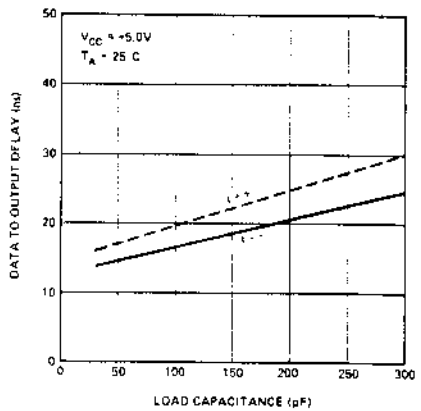
OUTPUT CURRENT VS. OUTPUT "LOW" VOLTAGE



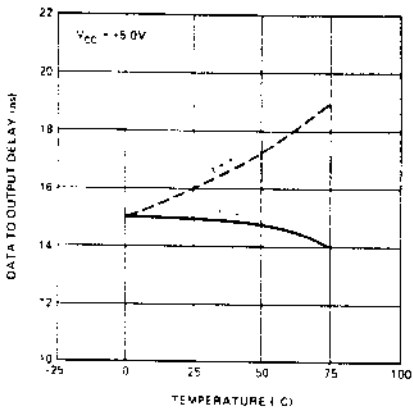
OUTPUT CURRENT VS. OUTPUT "HIGH" VOLTAGE



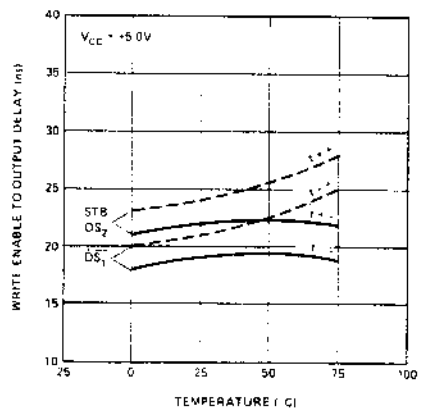
DATA TO OUTPUT DELAY VS. LOAD CAPACITANCE



DATA TO OUTPUT DELAY VS. TEMPERATURE

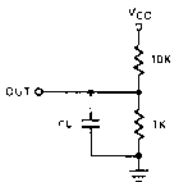
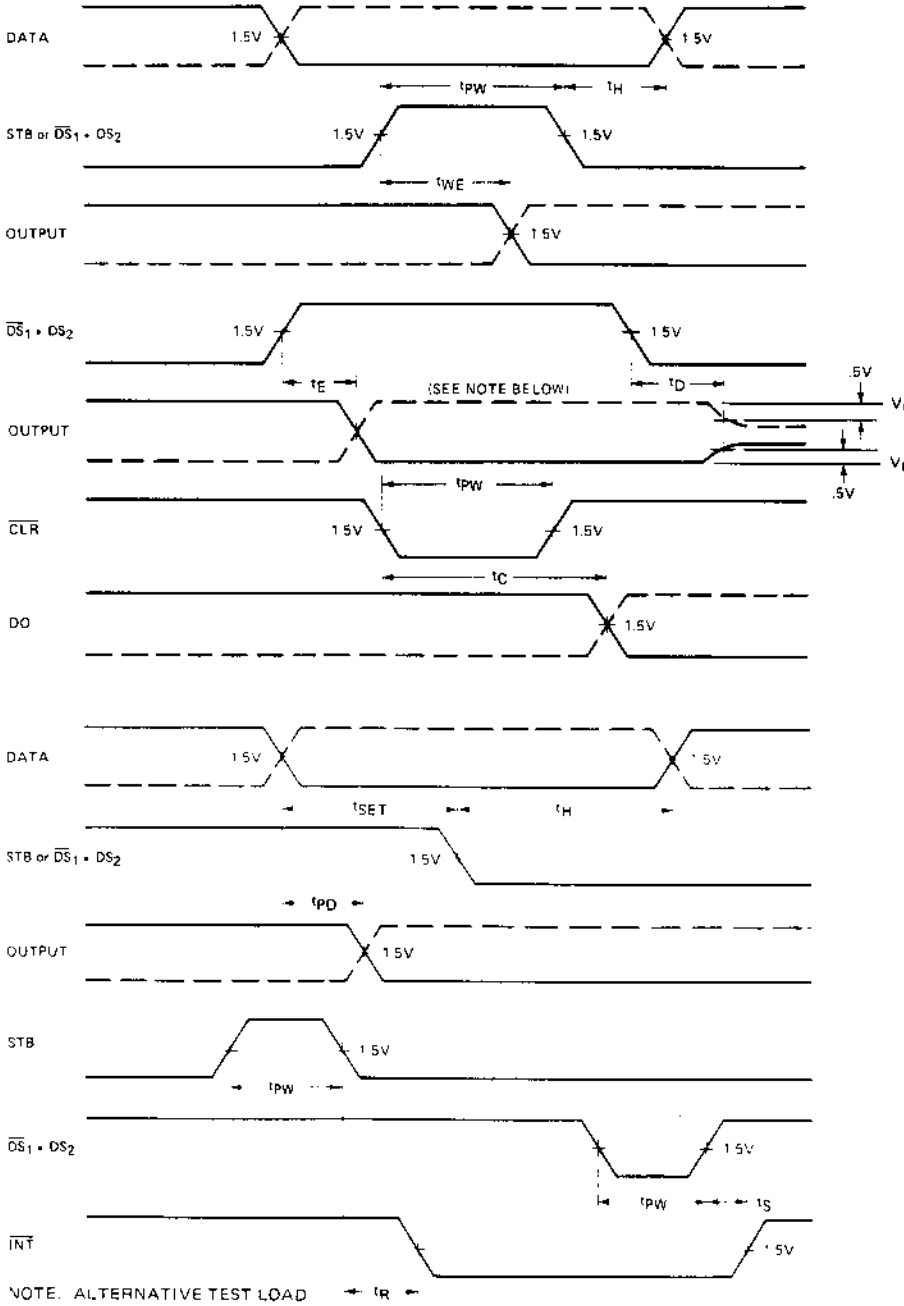


WRITE ENABLE TO OUTPUT DELAY VS. TEMPERATURE



SCHOTTKY BIPOLAR 8212

Timing Diagram



SCHOTTKY BIPOLAR 8212

A.C. Characteristics

$T_A = 0^\circ\text{C}$ to $+75^\circ\text{C}$ $V_{CC} = +5\text{V} \pm 5\%$

Symbol	Parameter	Limits			Unit	Test Conditions
		Min.	Typ.	Max.		
t_{pw}	Pulse Width	30			ns	
t_{pd}	Data To Output Delay			30	ns	
t_{we}	Write Enable To Output Delay			40	ns	
t_{su}	Data Setup Time	15			ns	
t_h	Data Hold Time	20			ns	
t_r	Reset To Output Delay			40	ns	
t_s	Set To Output Delay			30	ns	
t_e	Output Enable/Disable Time			45	ns	
t_c	Clear To Output Delay			55	ns	

CAPACITANCE* $F = 1\text{ MHz}$ $V_{EAS} = 2.5\text{ V}$ $V_{CC} = +5\text{ V}$ $T_A = 25^\circ\text{C}$

Symbol	Test	LIMITS	
		Typ.	Max.
C_{IN}	DS, MD Input Capacitance	9 pF	12 pF
C_{IN}	DS ₂ , CK, ACK, DI, DI ₀ Input Capacitance	5 pF	9 pF
C_{OUT}	DO, DO ₂ Output Capacitance	8 pF	12 pF

*This parameter is sampled and not 100% tested.

Switching Characteristics

CONDITIONS OF TEST

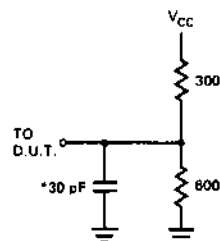
Input Pulse Amplitude = 2.5 V

Input Rise and Fall Times 5 ns

Between 1V and 2V Measurements made at 1.5V with 15 mA & 30 pF Test Load

TEST LOAD

15 mA & 30 pF



* INCLUDING JIG & PROBE CAPACITANCE

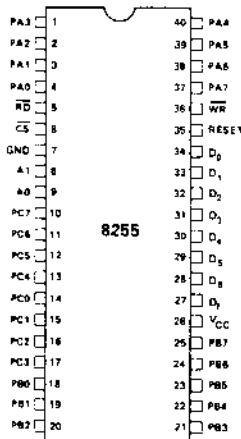
PROGRAMMABLE PERIPHERAL INTERFACE

- 24 Programmable I/O Pins
- Completely TTL Compatible
- Fully Compatible with MCS™ -8 and MCS™ -80 Microprocessor Families
- Direct Bit Set/Reset Capability Easing Control Application Interface
- 40 Pin Dual In-Line Package
- Reduces System Package Count

The 8255 is a general purpose programmable I/O device designed for use with both the 8008 and 8080 microprocessors. It has 24 I/O pins which may be individually programmed in two groups of twelve and used in three major modes of operation. In the first mode (Mode 0), each group of twelve I/O pins may be programmed in sets of 4 to be input or output. In Mode 1, the second mode, each group may be programmed to have 8 lines of input or output. Of the remaining four pins three are used for handshaking and interrupt control signals. The third mode of operation (Mode 2) is a Bidirectional Bus mode which uses 8 lines for a bidirectional bus, and five lines, borrowing one from the other group, for handshaking.

Other features of the 8255 include bit set and reset capability and the ability to source 1mA of current at 1.5 volts. This allows darlington transistors to be directly driven for applications such as printers and high voltage displays.

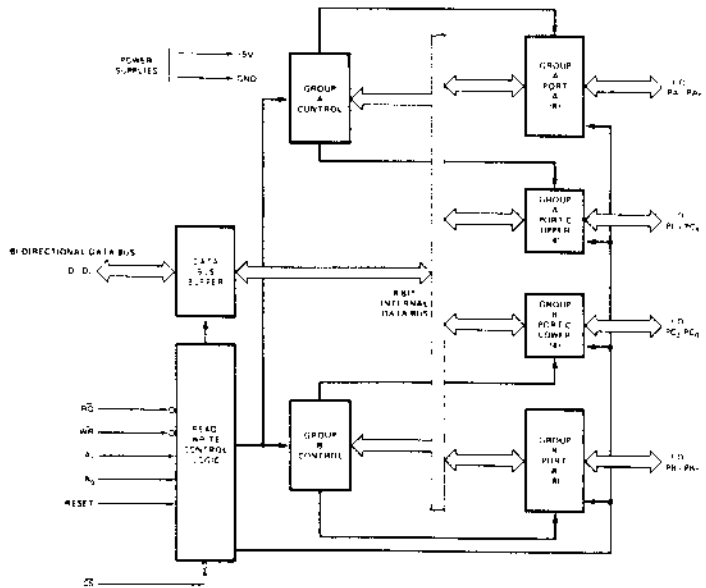
PIN CONFIGURATION



PIN NAMES

D ₇ -D ₀	DATA BUS (BI-DIRECTIONAL)
RESET	RESET INPUT
CS	CHIP SELECT
RD	READ INPUT
WR	WRITE INPUT
A ₀ , A ₁	PORT ADDRESS
PA ₇ -PA ₀	PORT A (BIT)
PB ₇ -PB ₀	PORT B (BIT)
PC ₇ -PC ₀	PORT C (BIT)
V _{CC}	+5 VOLTS
GND	0 VOLTS

8255 BLOCK DIAGRAM



SILICON GATE MOS 8255

8255 BASIC FUNCTIONAL DESCRIPTION

General

The 8255 is a Programmable Peripheral Interface (PPI) device designed for use in 8080 Microcomputer Systems. Its function is that of a general purpose I/O component to interface peripheral equipment to the 8080 system bus. The functional configuration of the 8255 is programmed by the system software so that normally no external logic is necessary to interface peripheral devices or structures.

Data Bus Buffer

This 3-state, bi-directional, eight bit buffer is used to interface the 8255 to the 8080 system data bus. Data is transmitted or received by the buffer upon execution of INput or OUTput instructions by the 8080 CPU. Control Words and Status information are also transferred through the Data Bus buffer.

Read/Write and Control Logic

The function of this block is to manage all of the internal and external transfers of both Data and Control or Status words. It accepts inputs from the 8080 CPU Address and Control busses and in turn, issues commands to both of the Control Groups.

(CS)

Chip Select: A "low" on this input pin enables the communication between the 8255 and the 8080 CPU.

(RD)

Read: A "low" on this input pin enables the 8255 to send the Data or Status information to the 8080 CPU on the Data Bus. In essence, it allows the 8080 CPU to "read from" the 8255.

(WR)

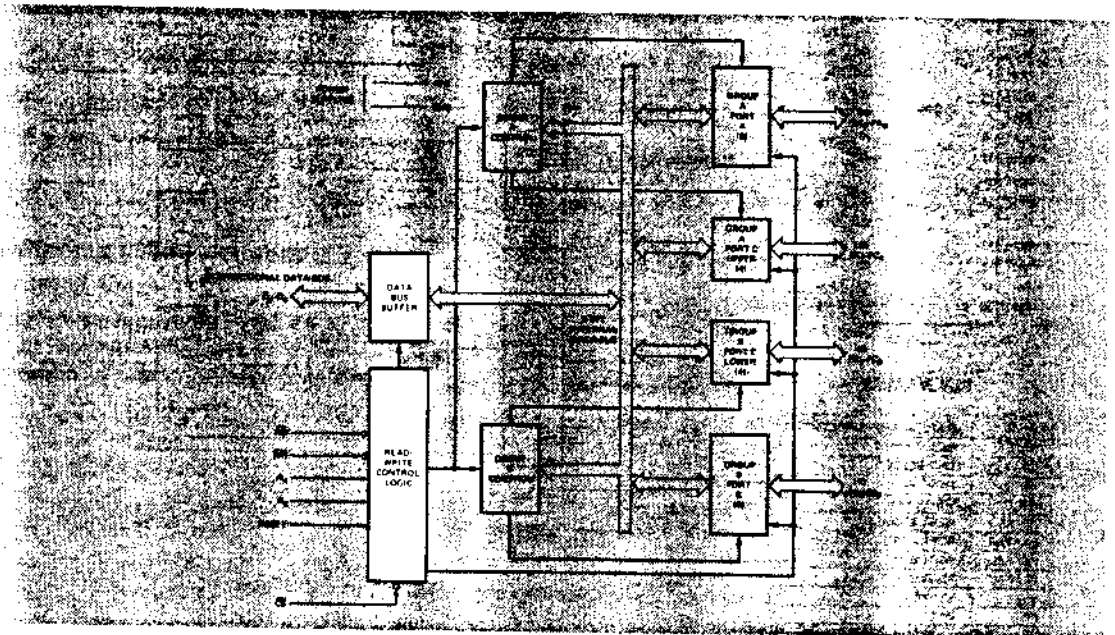
Write: A "low" on this input pin enables the 8080 CPU to write Data or Control words into the 8255.

(A₀ and A₁)

Port Select 0 and Port Select 1: These input signals, in conjunction with the RD and WR inputs, control the selection of one of the three ports or the Control Word Register. They are normally connected to the least significant bits of the Address Bus (A₀ and A₁).

8255 BASIC OPERATION

A ₁	A ₀	RD	WR	CS	INPUT OPERATION (READ)
0	0	0	1	0	PORT A = DATA BUS
0	1	0	1	0	PORT B = DATA BUS
1	0	0	1	0	PORT C = DATA BUS
					OUTPUT OPERATION (WRITE)
0	0	1	0	0	DATA BUS = PORT A
0	1	1	0	0	DATA BUS = PORT B
1	0	1	0	0	DATA BUS = PORT C
1	1	1	0	0	DATA BUS = CONTROL
					DISABLE FUNCTION
X	X	X	X	1	DATA BUS = 3-STATE
1	1	0	1	0	ILLEGAL CONDITION



8255 Block Diagram

SILICON GATE MOS 8255

(RESET)

Reset: A "high" on this input clears all internal registers including the Control Register and all ports (A, B, C) are set to the input mode.

Group A and Group B Controls

The functional configuration of each port is programmed by the systems software. In essence, the 8080 CPU "outputs" a control word to the 8255. The control word contains information such as "mode", "bit set", "bit reset" etc. that initializes the functional configuration of the 8255.

Each of the Control blocks (Group A and Group B) accepts "commands" from the Read/Write Control Logic, receives "control words" from the internal data bus and issues the proper commands to its associated ports.

Control Group A — Port A and Port C upper (C7-C4)

Control Group B — Port B and Port C lower (C3-C0)

The Control Word Register can **Only** be written into. No Read operation of the Control Word Register is allowed.

Ports A, B, and C

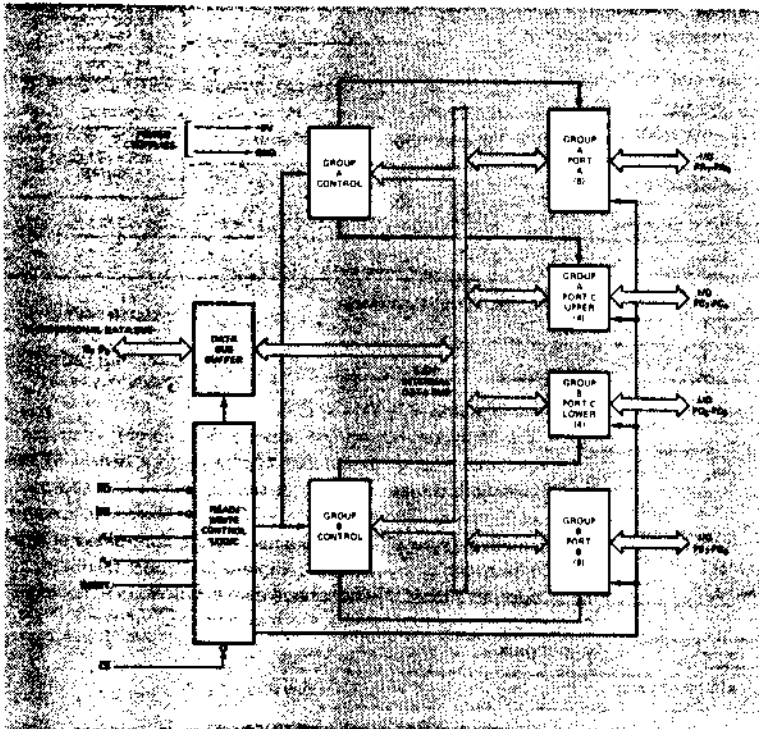
The 8255 contains three 8-bit ports (A, B, and C). All can be configured in a wide variety of functional characteristics by the system software but each has its own special features or "personality" to further enhance the power and flexibility of the 8255.

Port A: One 8-bit data output latch/buffer and one 8-bit data input latch.

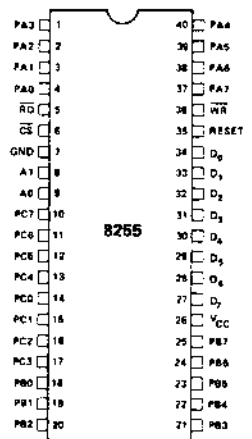
Port B: One 8-bit data input/output latch/buffer and one 8-bit data input buffer.

Port C: One 8-bit data output latch/buffer and one 8-bit data input buffer (no latch for input). This port can be divided into two 4-bit ports under the mode control. Each 4-bit port contains a 4-bit latch and it can be used for the control signal outputs and status signal inputs in conjunction with Ports A and B.

8255 BLOCK DIAGRAM



PIN CONFIGURATION



PIN NAMES

D ₇ -D ₀	DATA BUS (BI-DIRECTIONAL)
RESET	RESET INPUT
CS	CHIP SELECT
RD	READ INPUT
WR	WRITE INPUT
A ₀ , A ₁	PORT ADDRESS
PA ₇ -PA ₀	PORT A (BIT)
PB ₇ -PB ₀	PORT B (BIT)
PC ₇ -PC ₀	PORT C (BIT)
V _{cc}	+5 VOLTS
GND	0 VOLTS

8255 DETAILED OPERATIONAL DESCRIPTION

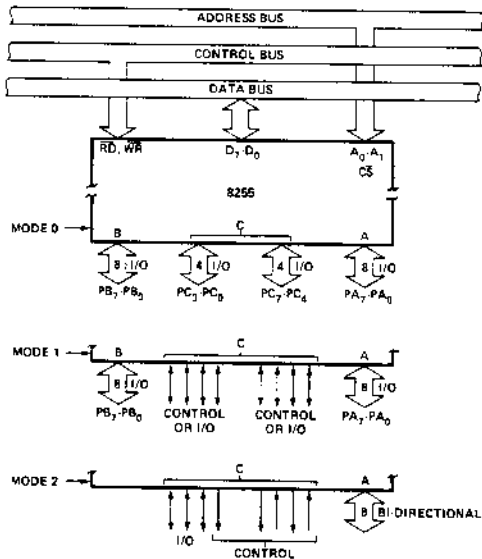
Mode Selection

There are three basic modes of operation that can be selected by the system software:

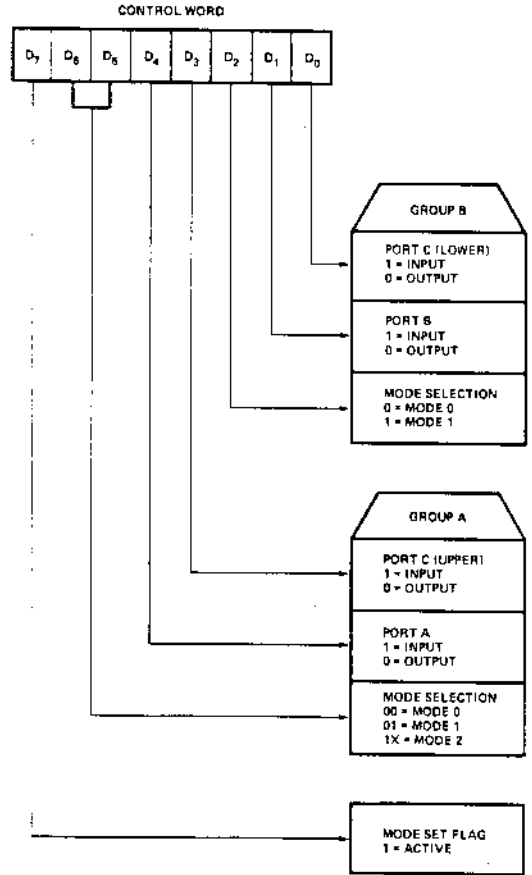
- Mode 0 – Basic Input/Output
- Mode 1 – Strobed Input/Output
- Mode 2 – Bi-Directional Bus

When the RESET input goes "high" all ports will be set to the Input mode (i.e., all 24 lines will be in the high impedance state). After the RESET is removed the 8255 can remain in the Input mode with no additional initialization required. During the execution of the system program any of the other modes may be selected using a single OUTPUT instruction. This allows a single 8255 to service a variety of peripheral devices with a simple software maintenance routine.

The modes for Port A and Port B can be separately defined, while Port C is divided into two portions as required by the Port A and Port B definitions. All of the output registers, including the status flip-flops, will be reset whenever the mode is changed. Modes may be combined so that their functional definition can be "tailored" to almost any I/O structure. For instance: Group B can be programmed in Mode 0 to monitor simple switch closings or display computational results, Group A could be programmed in Mode 1 to monitor a keyboard or tape reader on an interrupt-driven basis.



Basic Mode Definitions and Bus Interface

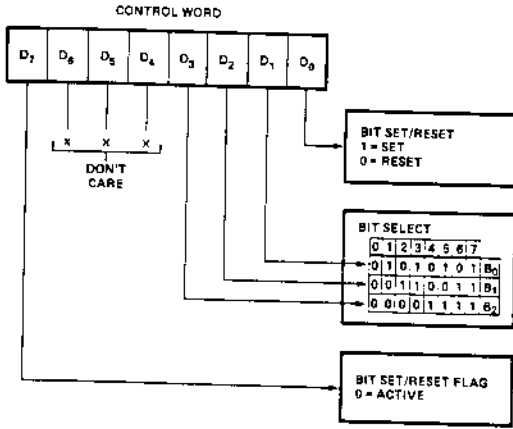


Mode Definition Format

The Mode definitions and possible Mode combinations may seem confusing at first but after a cursory review of the complete device operation a simple, logical I/O approach will surface. The design of the 8255 has taken into account things such as efficient PC board layout, control signal definition vs PC layout and complete functional flexibility to support almost any peripheral device with no external logic. Such design represents the maximum use of the available pins.

Single Bit Set/Reset Feature

Any of the eight bits of Port C can be Set or Reset using a single OUTPUT instruction. This feature reduces software requirements in Control-based applications.



Bit Set/Reset Format

When Port C is being used as status/control for Port A or B, these bits can be set or reset by using the Bit Set/Reset operation just as if they were data output ports.

Interrupt Control Functions

When the 8255 is programmed to operate in Mode 1 or Mode 2, control signals are provided that can be used as interrupt request inputs to the CPU. The interrupt request signals, generated from Port C, can be inhibited or enabled by setting or resetting the associated INTE flip-flop, using the Bit set/reset function of Port C.

This function allows the Programmer to disallow or allow a specific I/O device to interrupt the CPU without effecting any other device in the interrupt structure.

INTE flip-flop definition:

(BIT-SET) – INTE is SET – Interrupt enable

(BIT-RESET) – INTE is RESET – Interrupt disable

Note: All Mask flip-flops are automatically reset during mode selection and device Reset.

Operating Modes

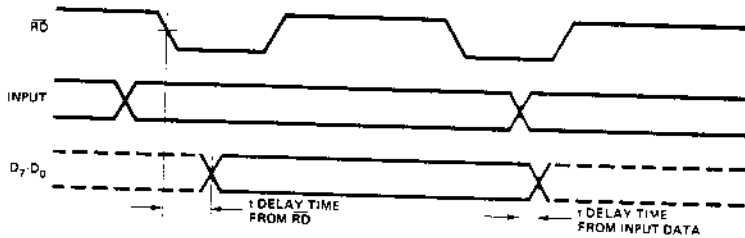
Mode 0 (Basic Input/Output)

This functional configuration provides simple Input and Output operations for each of the three ports. No "hand-shaking" is required, data is simply written to or read from a specified port.

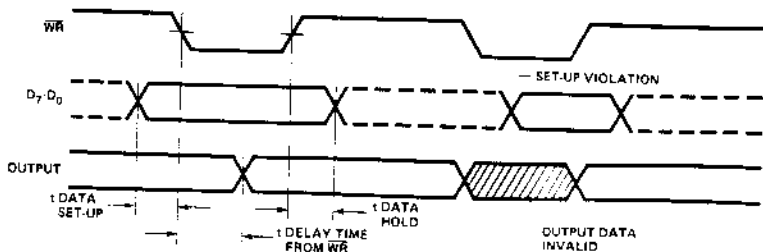
Mode 0 Basic Functional Definitions:

- Two 8-bit ports and two 4-bit ports.
- Any port can be input or output.
- Outputs are latched.
- Inputs are not latched.
- 16 different Input/Output configurations are possible in this Mode.

BASIC INPUT TIMING (D₇-D₀ FOLLOWS INPUT, NO LATCHING)



BASIC OUTPUT TIMING (OUTPUTS LATCHED)



Mode 0 Timing

SILICON GATE MOS 8255

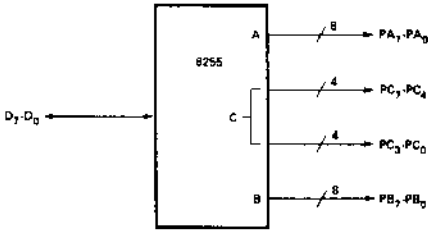
MODE 0 PORT DEFINITION CHART

A		B		GROUP A			GROUP B	
D ₄	D ₃	D ₁	D ₀	PORT A	PORT C (UPPER)	#	PORT B	PORT C (LOWER)
0	0	0	0	OUTPUT	OUTPUT	0	OUTPUT	OUTPUT
0	0	0	1	OUTPUT	OUTPUT	1	OUTPUT	INPUT
0	0	1	0	OUTPUT	OUTPUT	2	INPUT	OUTPUT
0	0	1	1	OUTPUT	OUTPUT	3	INPUT	INPUT
0	1	0	0	OUTPUT	INPUT	4	OUTPUT	OUTPUT
0	1	0	1	OUTPUT	INPUT	5	OUTPUT	INPUT
0	1	1	0	OUTPUT	INPUT	6	INPUT	OUTPUT
0	1	1	1	OUTPUT	INPUT	7	INPUT	INPUT
1	0	0	0	INPUT	OUTPUT	8	OUTPUT	OUTPUT
1	0	0	1	INPUT	OUTPUT	9	OUTPUT	INPUT
1	0	1	0	INPUT	OUTPUT	10	INPUT	OUTPUT
1	0	1	1	INPUT	OUTPUT	11	INPUT	INPUT
1	1	0	0	INPUT	INPUT	12	OUTPUT	OUTPUT
1	1	0	1	INPUT	INPUT	13	OUTPUT	INPUT
1	1	1	0	INPUT	INPUT	14	INPUT	OUTPUT
1	1	1	1	INPUT	INPUT	15	INPUT	INPUT

MODE 0 CONFIGURATIONS

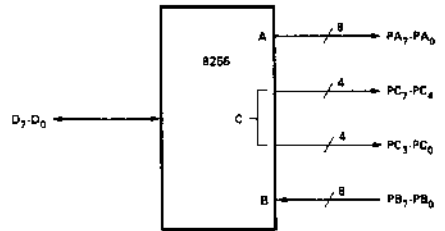
CONTROL WORD #0

D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	0	0	0	0	0



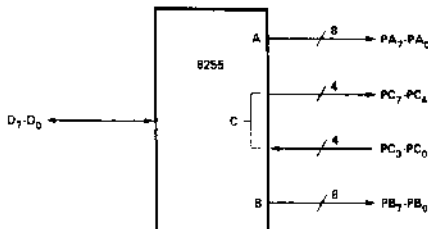
CONTROL WORD #2

D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	0	0	0	1	0



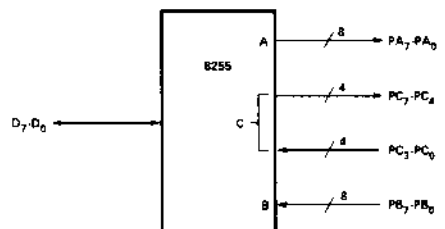
CONTROL WORD #1

D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	0	0	0	0	1



CONTROL WORD #3

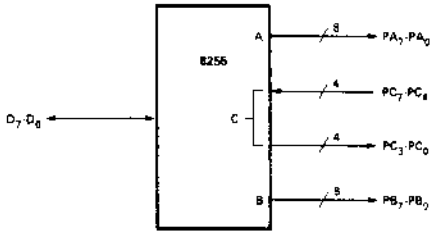
D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	0	0	0	1	1



SILICON GATE MOS 8255

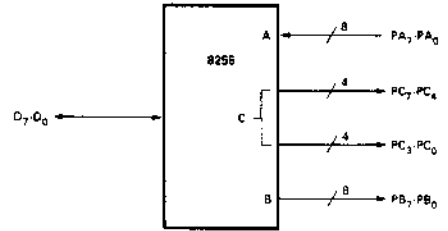
CONTROL WORD #4

D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	0	1	0	0	0



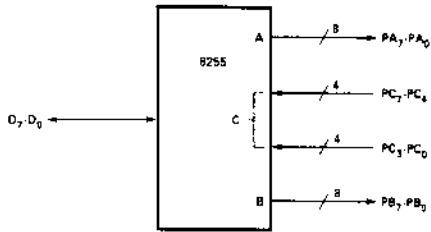
CONTROL WORD #8

D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	1	0	0	0	0



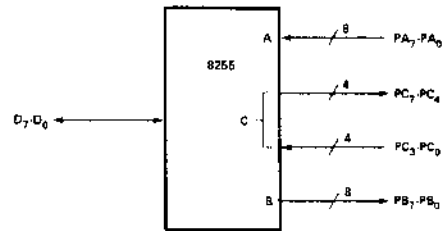
CONTROL WORD #5

D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	0	1	0	0	1



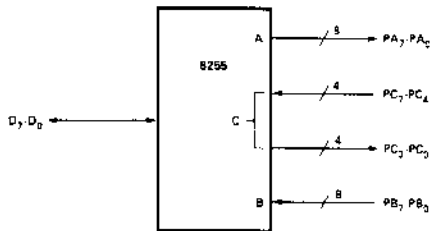
CONTROL WORD #9

D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	1	0	0	0	1



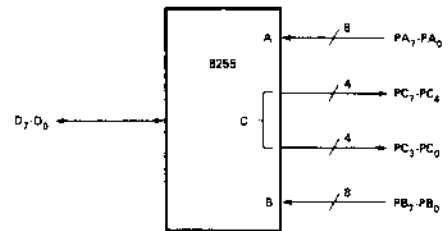
CONTROL WORD #6

D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	0	1	0	1	0



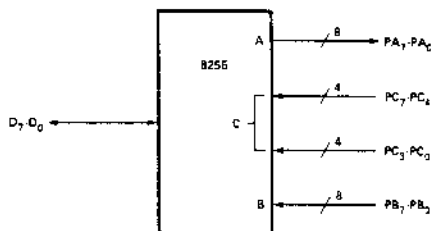
CONTROL WORD #10

D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	1	0	0	1	0



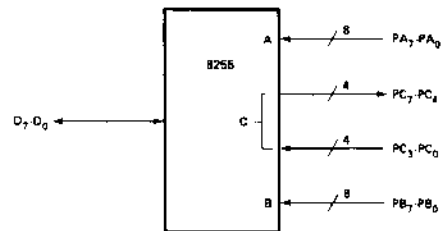
CONTROL WORD #7

D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	0	1	0	1	1

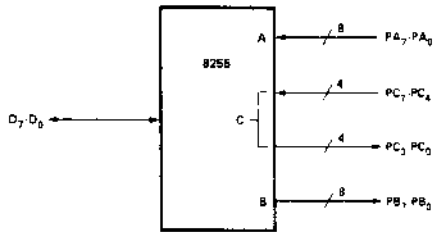
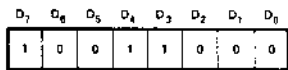


CONTROL WORD #11

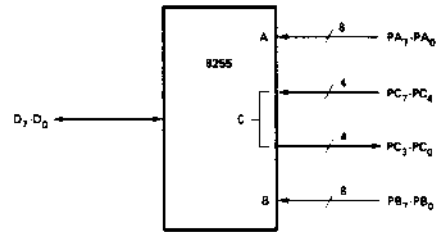
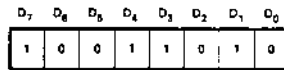
D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀
1	0	0	1	0	0	1	1



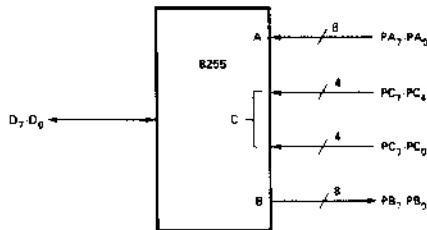
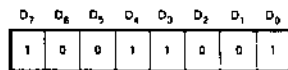
CONTROL WORD #12



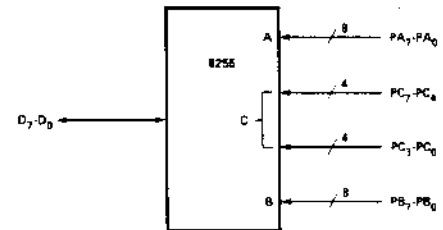
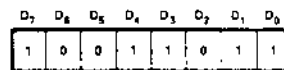
CONTROL WORD #14



CONTROL WORD #13



CONTROL WORD #15



Operating Modes

Mode 1 (Strobed Input/Output)

This functional configuration provides a means for transferring I/O data to or from a specified port in conjunction with strobes or "handshaking" signals. In Mode 1, Port A and Port B use the lines on Port C to generate or accept these "handshaking" signals.

Mode 1 Basic Functional Definitions:

- Two Groups (Group A and Group B)
- Each group contains one 8-bit data port and one 4-bit control/data port.
- The 8-bit data port can be either input or output. Both inputs and outputs are latched.
- The 4-bit port is used for control and status of the 8-bit data port.

Input Control Signal Definition

STB (Strobe Input)

A "low" on this input loads data into the input latch.

IBF (Input Buffer Full F/F)

A "high" on this output indicates that the data has been loaded into the input latch; in essence, an acknowledgement. IBF is set by the falling edge of the STB input and is reset by the rising edge of the RD input.

INTR (Interrupt Request)

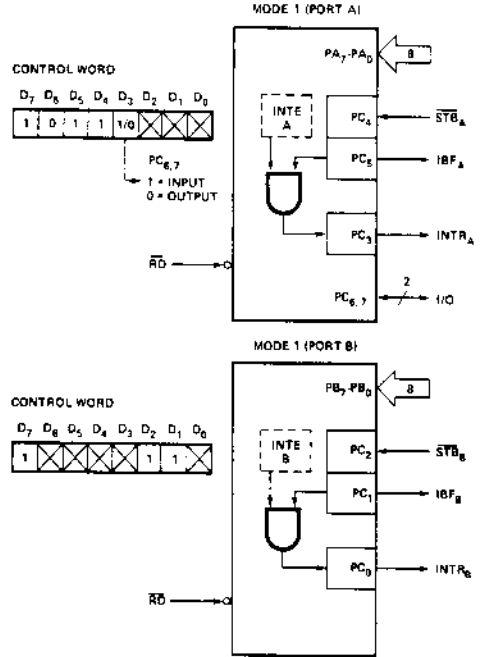
A "high" on this output can be used to interrupt the CPU when an input device is requesting service. INTR is set by the rising edge of STB if IBF is a "one" and INTE is a "one". It is reset by the falling edge of RD. This procedure allows an input device to request service from the CPU by simply strobing its data into the port.

INTE A

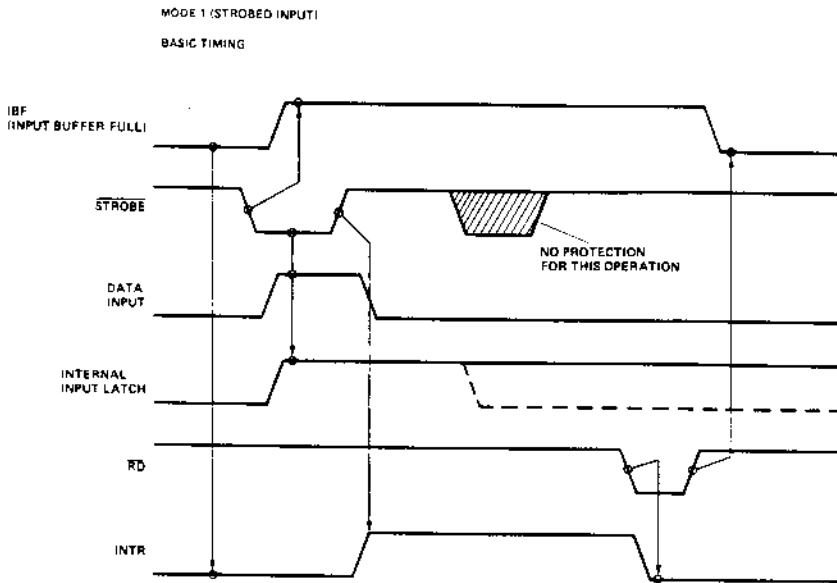
Controlled by bit set/reset of PC₄.

INTE B

Controlled by bit set/reset of PC₂.



Mode 1 Input



Basic Timing Input

Output Control Signal Definition

OB \bar{F} (Output Buffer Full F/F)

The $\bar{O}BF$ output will go "low" to indicate that the CPU has written data out to the specified port. The OBF F/F will be set by the rising edge of the WR input and reset by the falling edge of the ACK input signal.

ACK (Acknowledge Input)

A "low" on this input informs the 8255 that the data from Port A or Port B has been accepted. In essence, a response from the peripheral device indicating that it has received the data output by the CPU.

INTR (Interrupt Request)

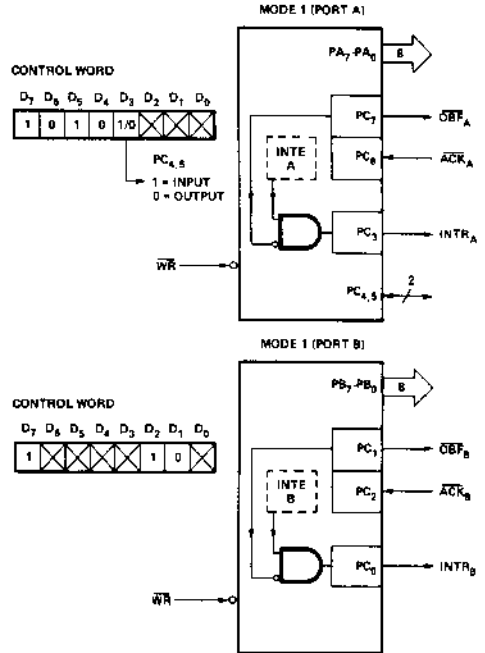
A "high" on this output can be used to interrupt the CPU when an output device has accepted data transmitted by the CPU. $INTR$ is set by the rising edge of ACK if $\bar{O}BF$ is a "one" and $INTE$ is a "one". It is reset by the falling edge of WR .

INTE A

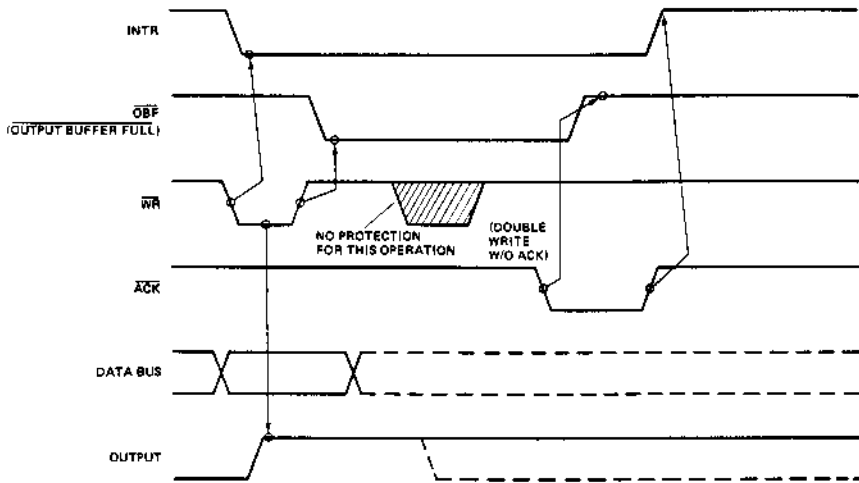
Controlled by bit set/reset of PC_6 .

INTE B

Controlled by bit set/reset of PC_2 .



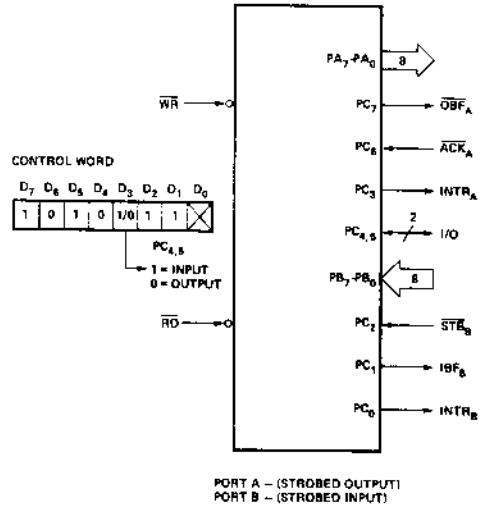
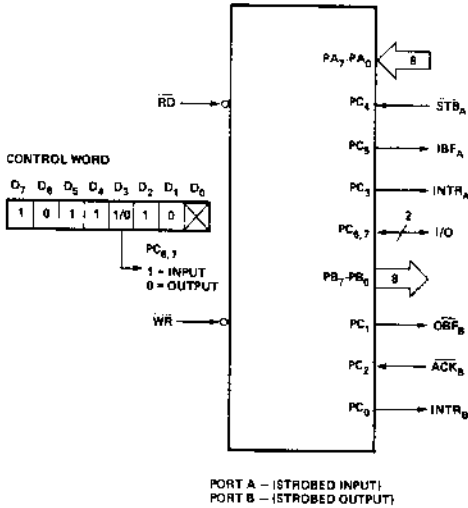
Mode 1 Output



SILICON GATE MOS 8255

Combinations of Mode 1

Port A and Port B can be individually defined as input or output in Mode 1 to support a wide variety of strobed I/O applications.



Operating Modes

Mode 2 (Strobed Bi-Directional Bus I/O)

This functional configuration provides a means for communicating with a peripheral device or structure on a single 8-bit bus for both transmitting and receiving data (bi-directional bus I/O). "Handshaking" signals are provided to maintain proper bus flow discipline in a similar manner to Mode 1. Interrupt generation and enable/disable functions are also available.

Mode 2 Basic Functional Definitions:

- Used in Group A only.
- One 8-bit, bi-directional bus Port (Port A) and a 5-bit control Port (Port C).
- Both inputs and outputs are latched.
- The 5-bit control port (Port C) is used for control and status for the 8-bit, bi-directional bus port (Port A).

Bi-Directional Bus I/O Control Signal Definition

INTR (Interrupt Request)

A high on this output can be used to interrupt the CPU for both input or output operations.

Output Operations

OBFB (Output Buffer Full)

The \overline{OBFB} output will go "low" to indicate that the CPU has written data out to Port A.

ACK (Acknowledge)

A "low" on this input enables the tri-state output buffer of Port A to send out the data. Otherwise, the output buffer will be in the high-impedance state.

INTE 1 (The INTE Flip-Flop associated with \overline{OBFB})

Controlled by bit set/reset of PC₆.

Input Operations

STB (Strobe Input)

A "low" on this input loads data into the input latch.

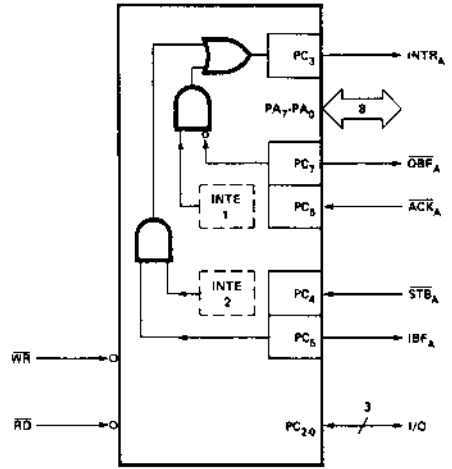
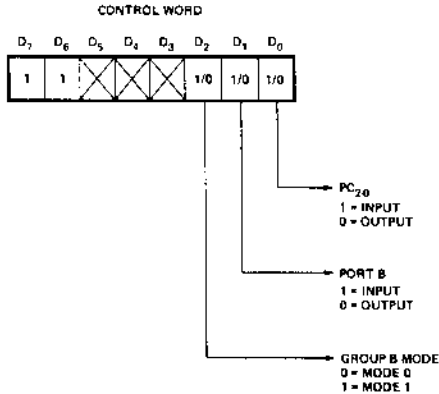
IBF (Input Buffer Full F/F)

A "high" on this output indicates that data has been loaded into the input latch.

INTE 2 (The INTE Flip-Flop associated with IBF)

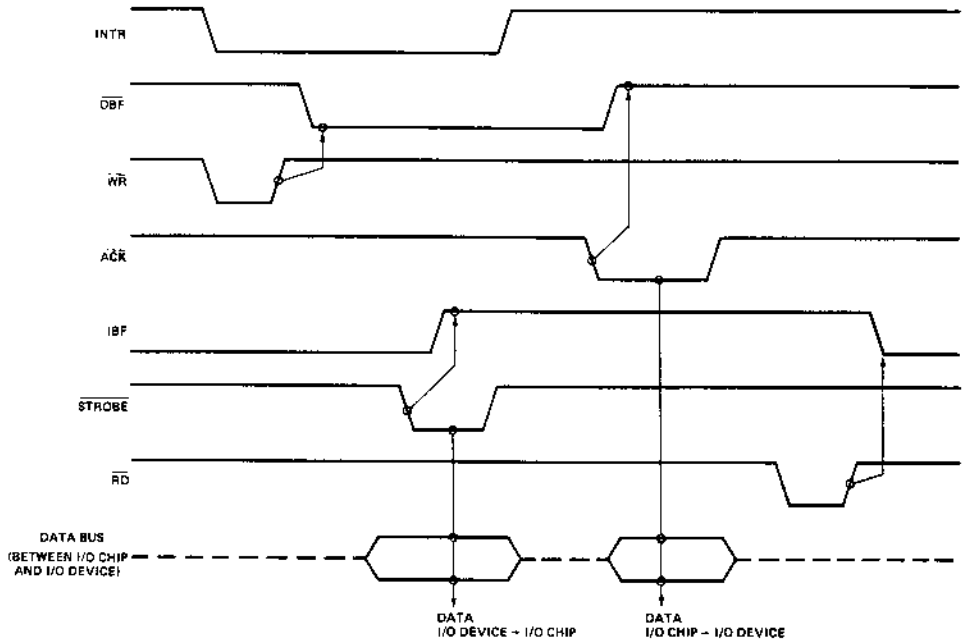
Controlled by bit set/reset of PC₄.

SILICON GATE MOS 8255



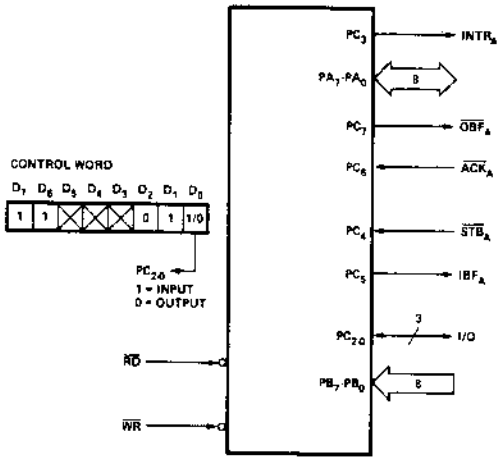
Mode 2 Control Word

Mode 2

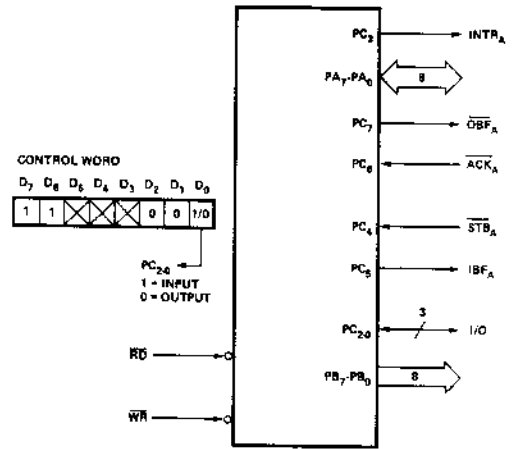


Mode 2 (Bi-directional) Timing

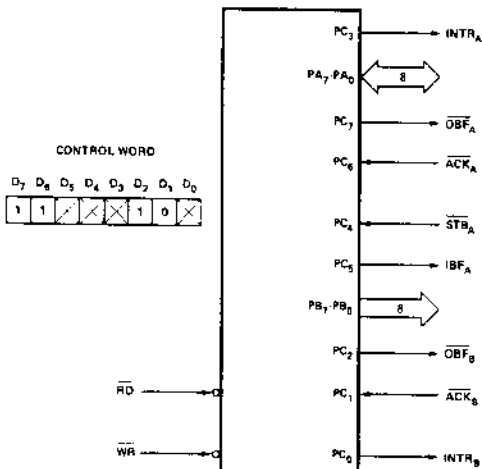
MODE 2 AND MODE 0 (INPUT)



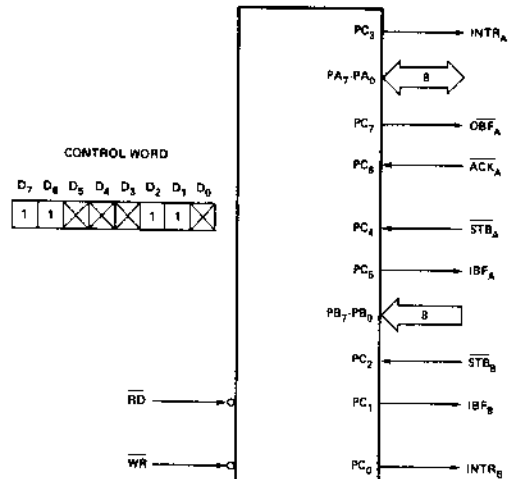
MODE 2 AND MODE 0 (OUTPUT)



MODE 2 AND MODE 1 (OUTPUT)



MODE 2 AND MODE 1 (INPUT)



MODE DEFINITION SUMMARY TABLE

	MODE 0		MODE 1		MODE 2	
	IN	OUT	IN	OUT	GROUP A ONLY	
PA ₀	IN	OUT	IN	OUT	↔	
PA ₁	IN	OUT	IN	OUT	↔	
PA ₂	IN	OUT	IN	OUT	↔	
PA ₃	IN	OUT	IN	OUT	↔	
PA ₄	IN	OUT	IN	OUT	↔	
PA ₅	IN	OUT	IN	OUT	↔	
PA ₆	IN	OUT	IN	OUT	↔	
PA ₇	IN	OUT	IN	OUT	↔	
PB ₀	IN	OUT	IN	OUT	—	
PB ₁	IN	OUT	IN	OUT	—	
PB ₂	IN	OUT	IN	OUT	—	
PB ₃	IN	OUT	IN	OUT	—	
PB ₄	IN	OUT	IN	OUT	—	
PB ₅	IN	OUT	IN	OUT	—	
PB ₆	IN	OUT	IN	OUT	—	
PB ₇	IN	OUT	IN	OUT	—	
PC ₀	IN	OUT	INTR _B	INTR _B	I/O	
PC ₁	IN	OUT	IBF _B	OBFB	I/O	
PC ₂	IN	OUT	STB _B	ACK _B	I/O	
PC ₃	IN	OUT	INTR _A	INTR _A	INTR _A	
PC ₄	IN	OUT	STB _A	I/O	STB _A	
PC ₅	IN	OUT	IBF _A	I/O	IBF _A	
PC ₆	IN	OUT	I/O	ACK _A	ACK _A	
PC ₇	IN	OUT	I/O	OBFA	OBFA	

Special Mode Combination Considerations

There are several combinations of modes when not all of the bits in Port C are used for control or status. The remaining bits can be used as follows:

If Programmed as Inputs –

All input lines can be accessed during a normal Port C read.

If Programmed as Outputs –

Bits in C upper (PC₇-PC₄) must be individually accessed using the bit set/reset function.

Bits in C lower (PC₃-PC₀) can be accessed using the bit set/reset function or accessed as a threesome by writing into Port C.

Source Current Capability on Port B and Port C

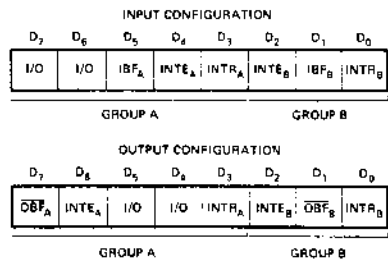
Any set of eight output buffers, selected randomly from Ports B and C can source 1mA at 1.5 volts. This feature allows the 8255 to directly drive Darlington type drivers and high-voltage displays that require such source current.

Reading Port C Status

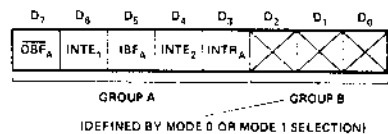
In Mode 0, Port C transfers data to or from the peripheral device. When the 8255 is programmed to function in Modes 1 or 2, Port C generates or accepts "hand-shaking" signals with the peripheral device. Reading the contents of Port C

allows the programmer to test or verify the "status" of each peripheral device and change the program flow accordingly.

There is no special instruction to read the status information from Port C. A normal read operation of Port C is executed to perform this function.



Mode 1 Status Word Format

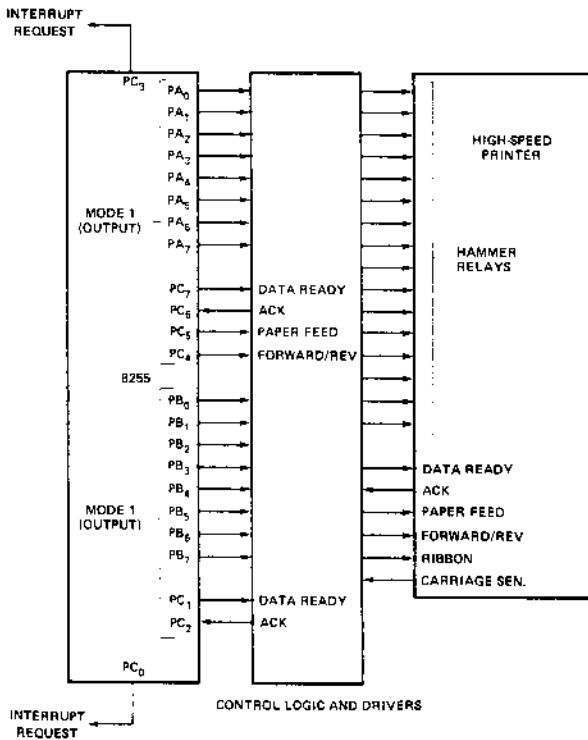


Mode 2 Status Word Format

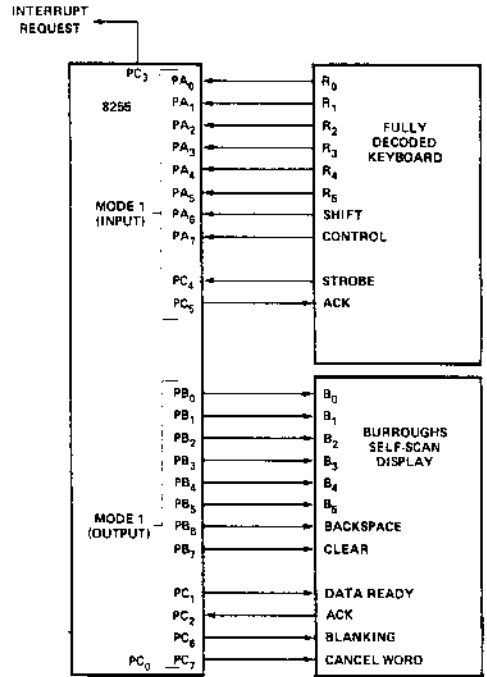
APPLICATIONS OF THE 8255

The 8255 is a very powerful tool for interfacing peripheral equipment to the 8080 microcomputer system. It represents the optimum use of available pins and is flexible enough to interface almost any I/O device without the need for additional external logic.

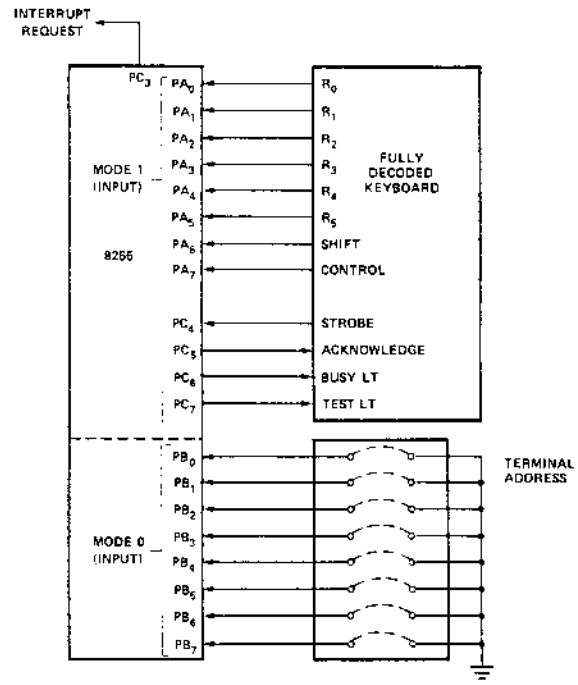
Each peripheral device in a Microcomputer system usually has a "service routine" associated with it. The routine manages the software interface between the device and the CPU. The functional definition of the 8255 is programmed by the I/O service routine and becomes an extension of the systems software. By examining the I/O devices interface characteristics for both data transfer and timing, and matching this information to the examples and tables in the Detailed Operational Description, a control word can easily be developed to initialize the 8255 to exactly "fit" the application. Here are a few examples of typical applications of the 8255.



Printer Interface

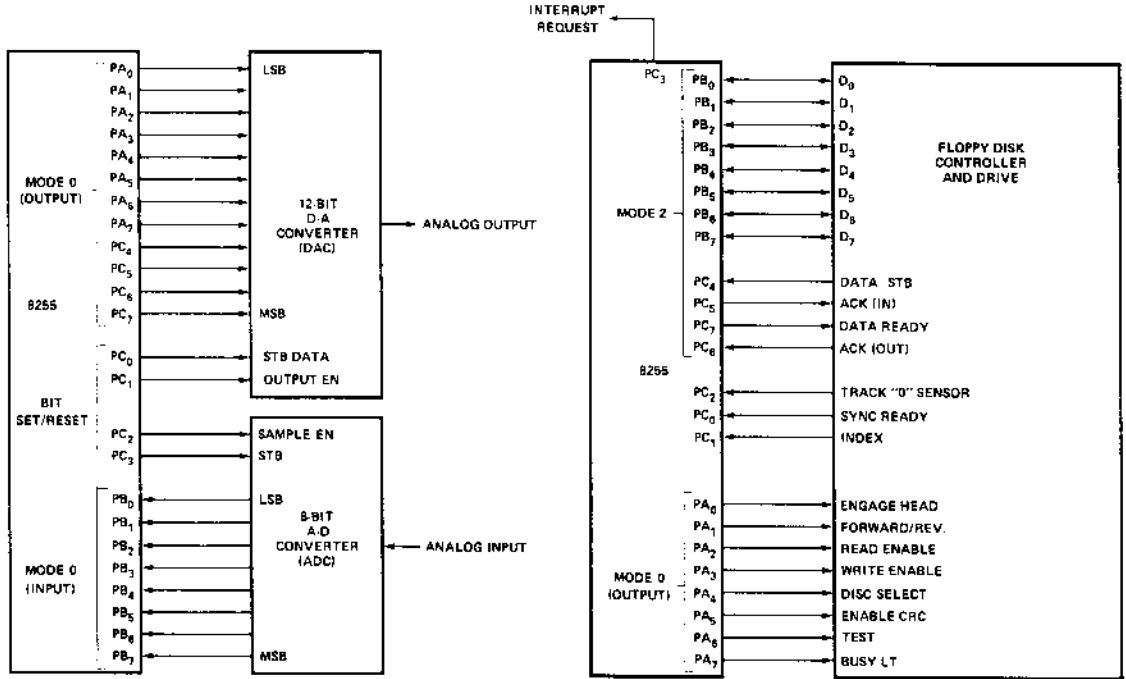


Keyboard and Display Interface



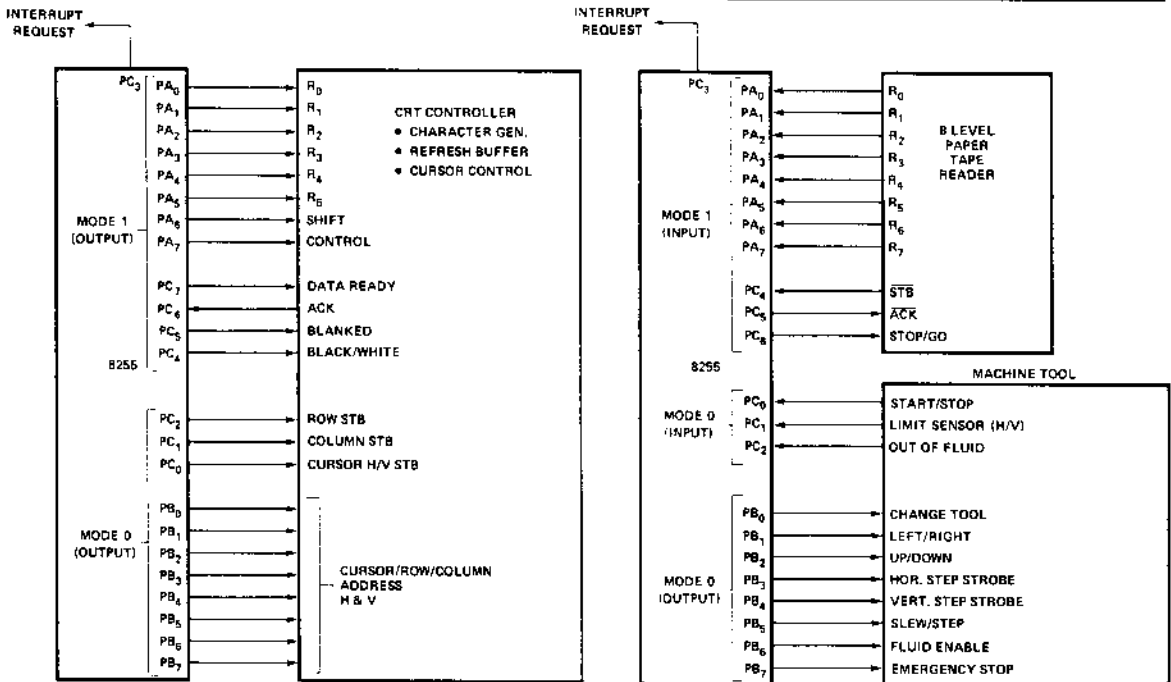
Keyboard and Terminal Address Interface

SILICON GATE MOS 8255



Digital to Analog, Analog to Digital

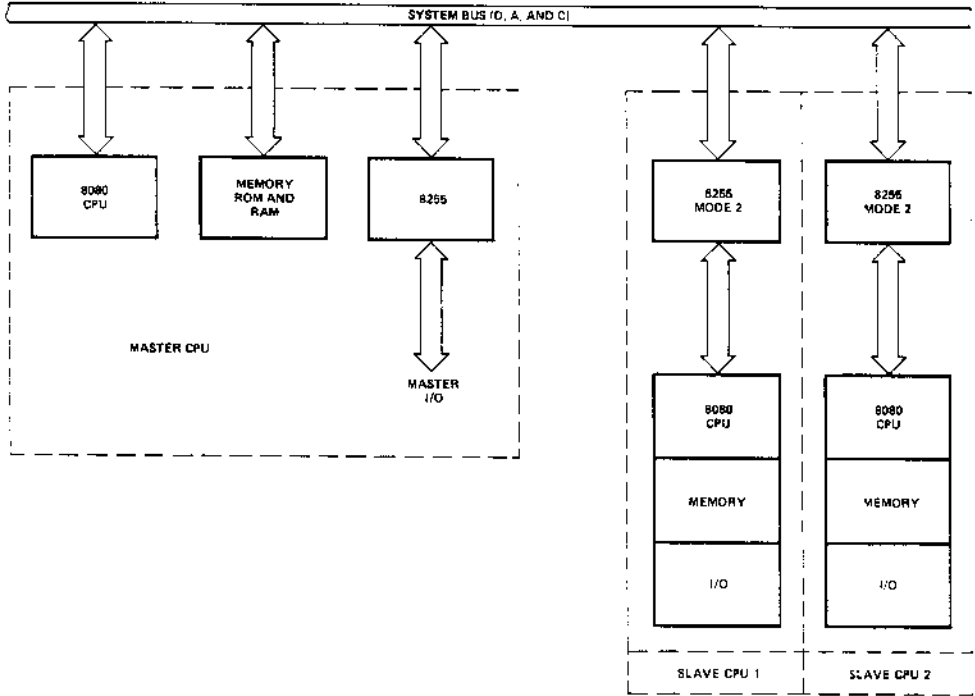
Basic Floppy Disc Interface



Basic CRT Controller Interface

Machine Tool Controller Interface

SILICON GATE MOS 8255



Distributed Intelligence Multi-Processor Interface

SILICON GATE MOS 8255

D.C. CHARACTERISTICS $T_A = 0^\circ\text{C}$ to 70°C ; $V_{CC} = +5\text{V} \pm 5\%$; $V_{SS} = 0\text{V}$

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
V_{IL}	Input Low Voltage			.8	V	
V_{IH}	Input High Voltage	2.0			V	
V_{OL}	Output Low Voltage			.4	V	$I_{OL} = 1.6\text{mA}$
V_{OH}	Output High Voltage	2.4			V	$I_{OH} = -50\mu\text{A}$ ($-100\mu\text{A}$ for D.B. Port)
$I_{OH}^{(1)}$	Darlington Drive Current		2.0		mA	$V_{OH} = 1.5\text{V}$, $R_{EXT} = 390\Omega$
I_{CC}	Power Supply Current		40		mA	

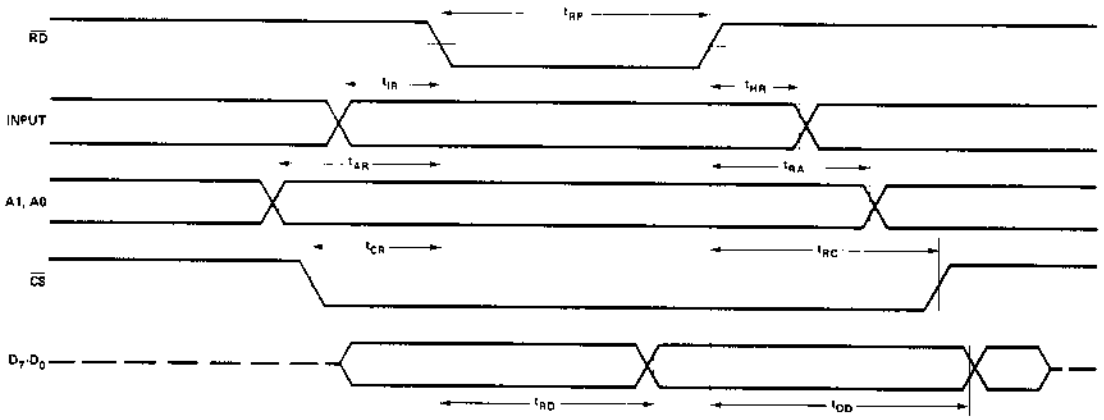
NOTE:

1. Available on 8 pins only.

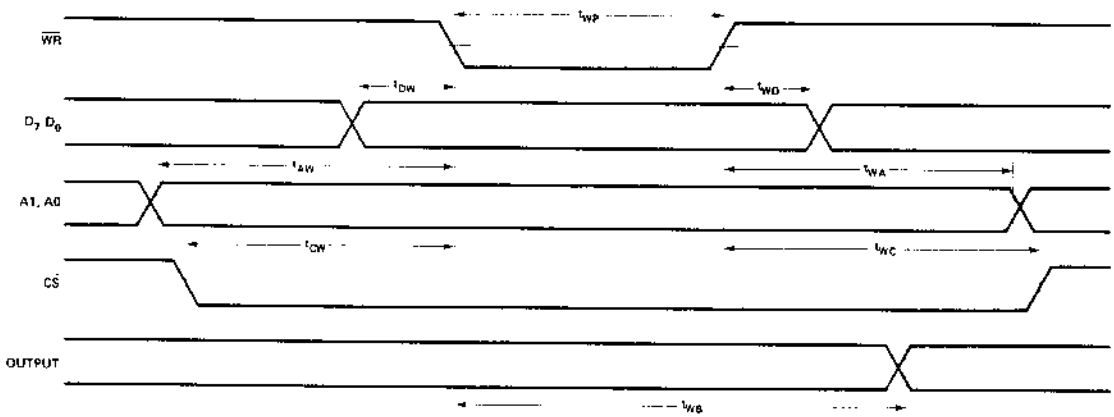
A.C. CHARACTERISTICS $T_A = 0^\circ\text{C}$ to 70°C ; $V_{CC} = +5\text{V} \pm 5\%$; $V_{SS} = 0\text{V}$

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
t_{WP}	Pulse Width of \overline{WR}			430	ns	
t_{DW}	Time D.B. Stable Before \overline{WR}	10			ns	
t_{WD}	Time D.B. Stable After \overline{WR}	65			ns	
t_{AW}	Time Address Stable Before \overline{WR}	20			ns	
t_{WA}	Time Address Stable After \overline{WR}	35			ns	
t_{CW}	Time CS Stable Before \overline{WR}	20			ns	
t_{WC}	Time CS Stable After \overline{WR}	35			ns	
t_{WB}	Delay From \overline{WR} To Output			500	ns	
t_{RP}	Pulse Width of \overline{RD}	430			ns	
t_{IR}	\overline{RD} Set-Up Time	50			ns	
t_{HR}	Input Hold Time	50			ns	
t_{RD}	Delay From $\overline{RD} = 0$ To System Bus	350			ns	
t_{OD}	Delay From $\overline{RD} = 1$ To System Bus	150			ns	
t_{AR}	Time Address Stable Before \overline{RD}	50			ns	
t_{CR}	Time \overline{CS} Stable Before \overline{RD}	50			ns	
t_{AK}	Width Of \overline{ACK} Pulse	500			ns	
t_{ST}	Width Of \overline{STB} Pulse	350			ns	
t_{PS}	Set-Up Time For Peripheral	150			ns	
t_{PH}	Hold Time For Peripheral	150			ns	
t_{RA}	Hold Time for A_1, A_0 After $\overline{RD} = 1$	379			ns	
t_{RC}	Hold Time For CS After $\overline{RD} = 1$	5			ns	
t_{AD}	Time From $\overline{ACK} = 0$ To Output (Mode 2)			500	ns	
t_{KD}	Time From $\overline{ACK} = 1$ To Output Floating			300	ns	
t_{WO}	Time From $\overline{WR} = 1$ To $\overline{OBF} = 0$			300	ns	
t_{AO}	Time From $\overline{ACK} = 0$ To $\overline{OBF} = 1$			500	ns	
t_{SI}	Time From $\overline{STB} = 0$ To \overline{IBF}			600	ns	
t_{RI}	Time From $\overline{RD} = 1$ To $\overline{IBF} = 0$			300	ns	

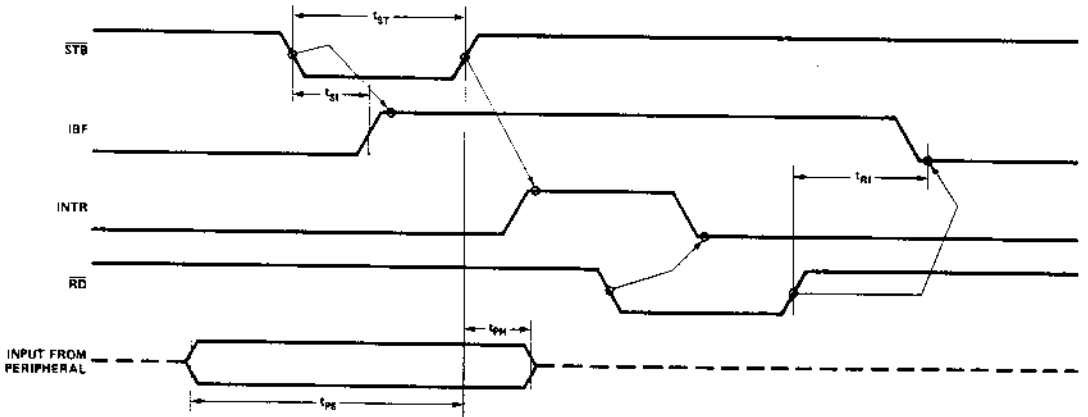
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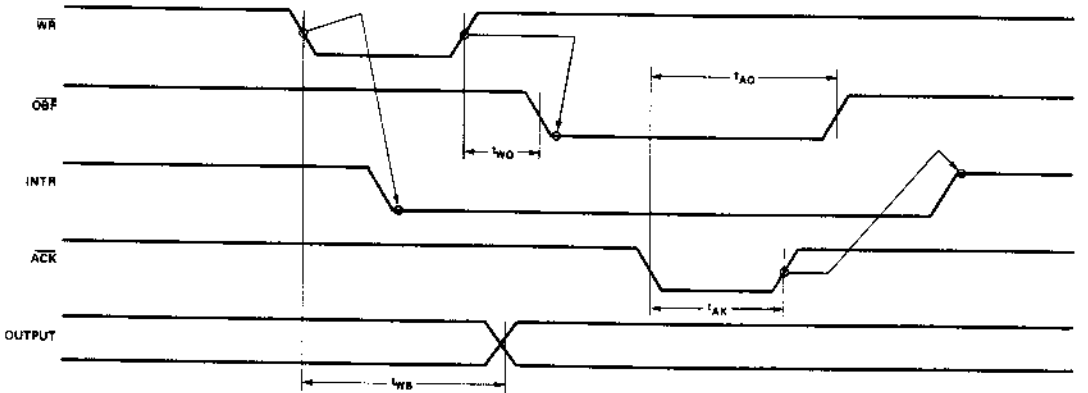
Mode 0 (Basic Input)



Mode 0 (Basic Output)

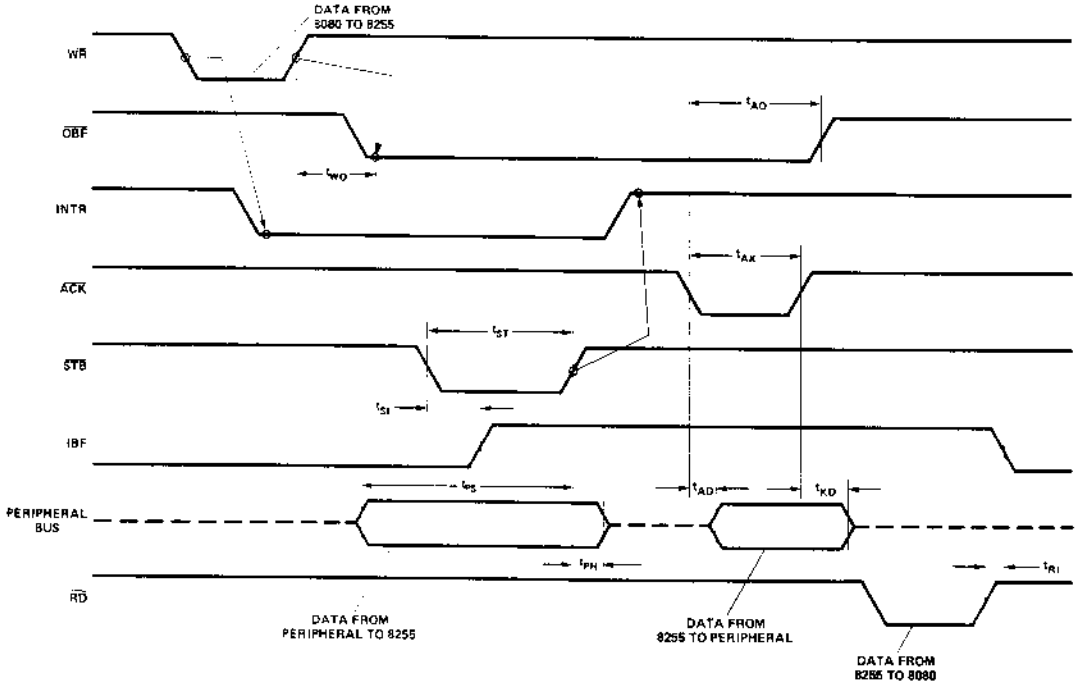


Mode 1 (Strobed Input)



Mode 1 (Strobed Output)

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Mode 2 (Bi-directional)